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Liu

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(54) **MEMORY CELLS**

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18, 2011, now Pat. No. 8,679,934, which is a division
of application No. 11/512,858, filed on Aug. 30, 2006,
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G11C 13/00 (2006.01)
H01L 27/24 (2006.01)

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None
See application file for complete search history.

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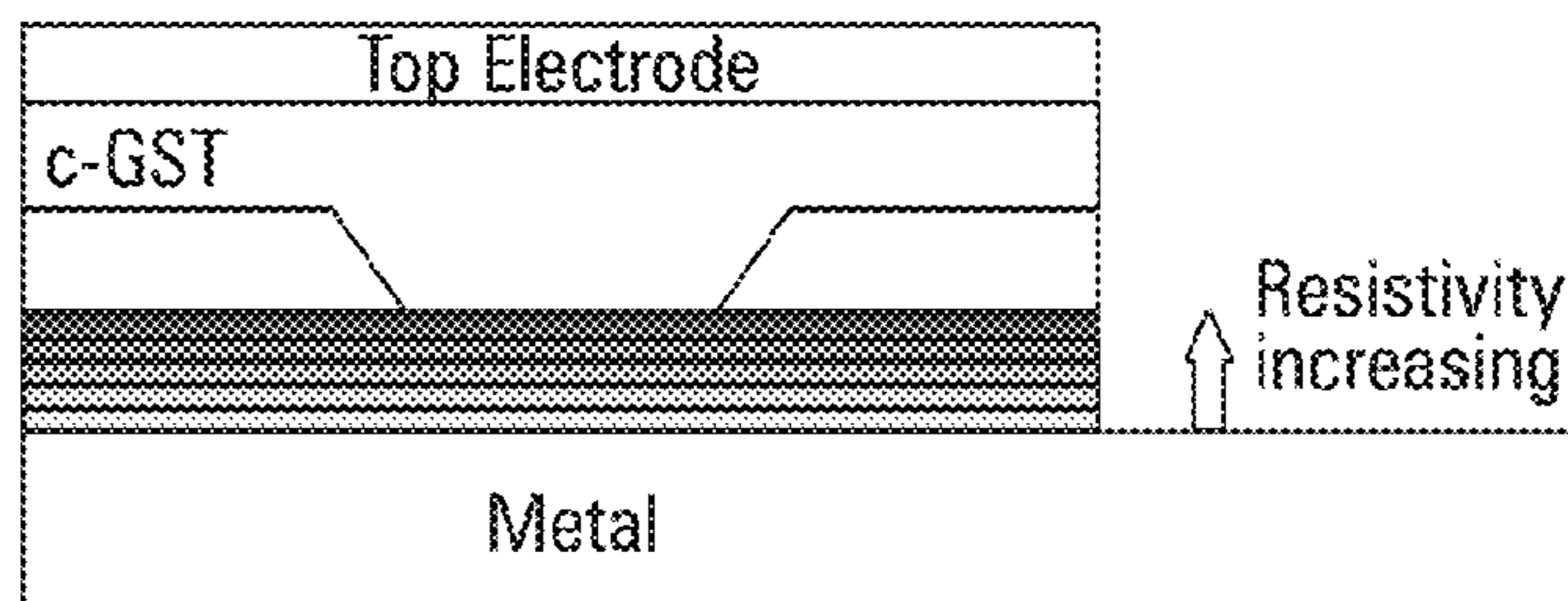
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PLLC

(57) **ABSTRACT**

Memory cells useful in phase change memory include a phase
change material between first and second electrode and hav-
ing a surface facing a surface of the second electrode. The
second electrode comprises a plurality of portions of material,
each portion having a respective distance from the surface of
the phase change material and each portion having a respec-
tive resistivity. A portion of the plurality of portions of mate-
rial farthest from the surface of the phase change material has
a lowest resistivity and a portion of the plurality of portions of
material closest to the surface of the phase change material
has a highest resistivity. The resistivity of each individual
portion is lower than the resistivity of each portion located
closer to the surface of the phase change material, and higher
than the resistivity of each portion located farther from the
surface of the phase change material.

20 Claims, 8 Drawing Sheets



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 (2013.01); *H01L 45/148* (2013.01); *H01L*
45/16 (2013.01); *G11C 2213/52* (2013.01)

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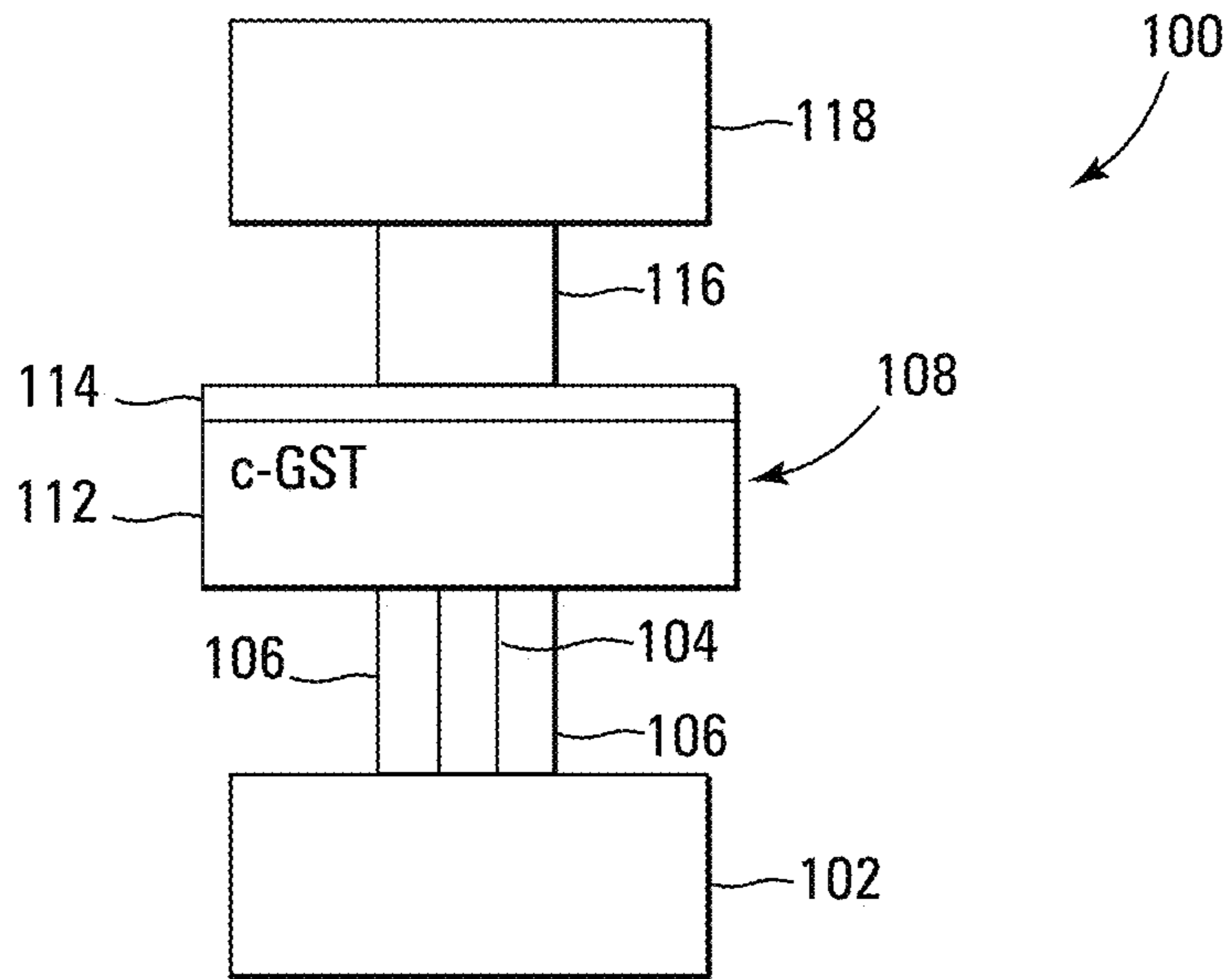


FIG. 1

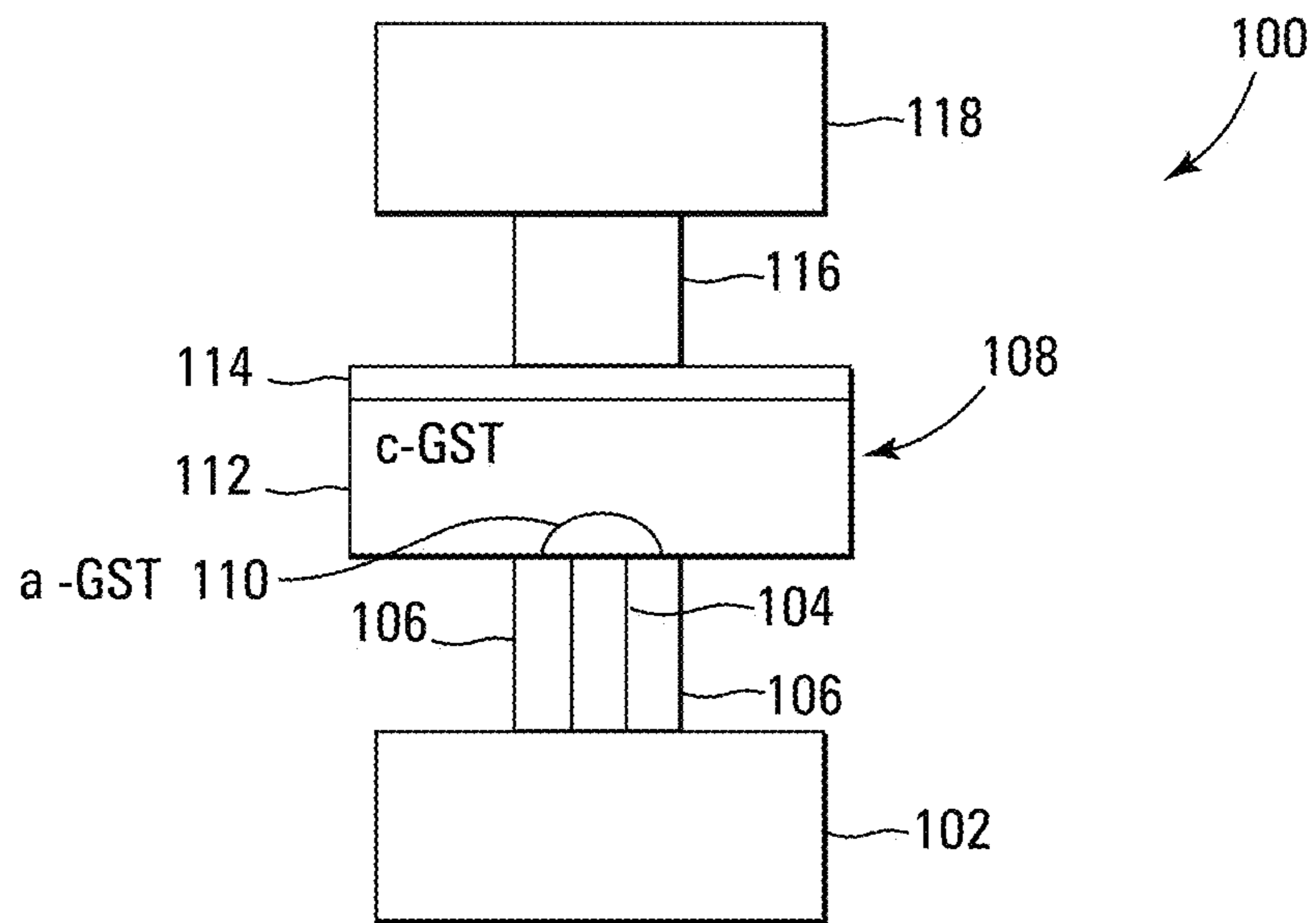


FIG. 2

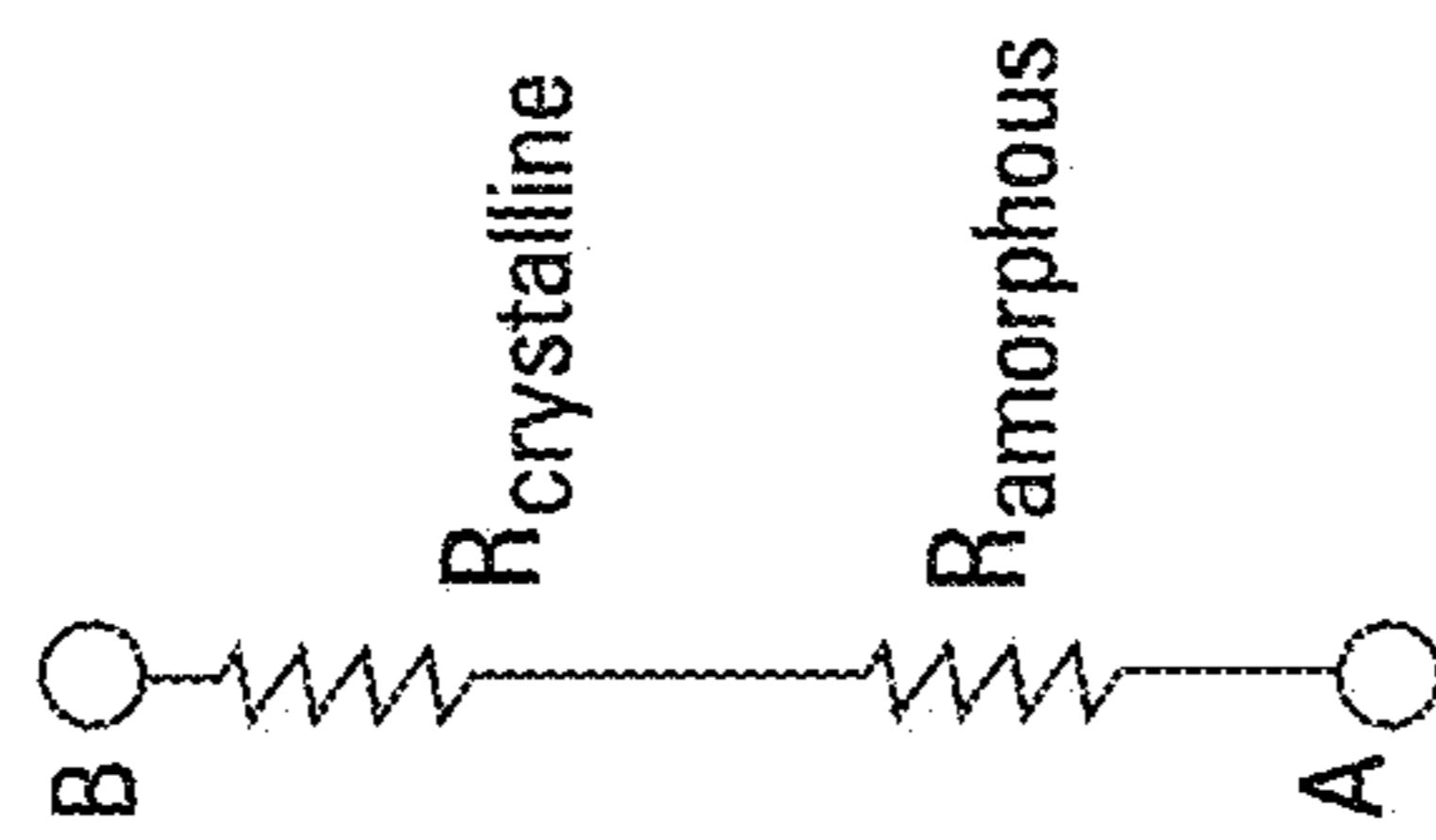
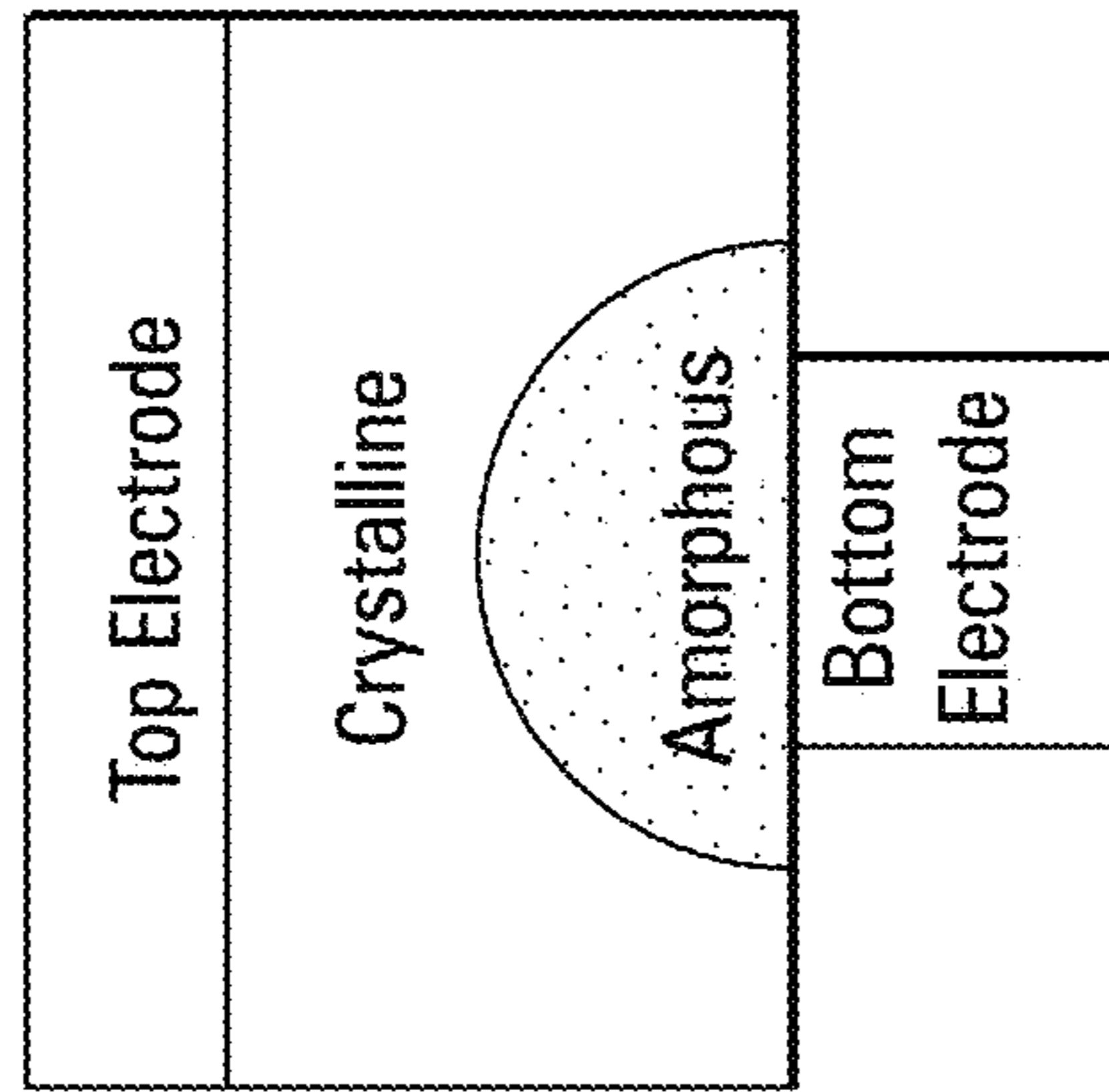
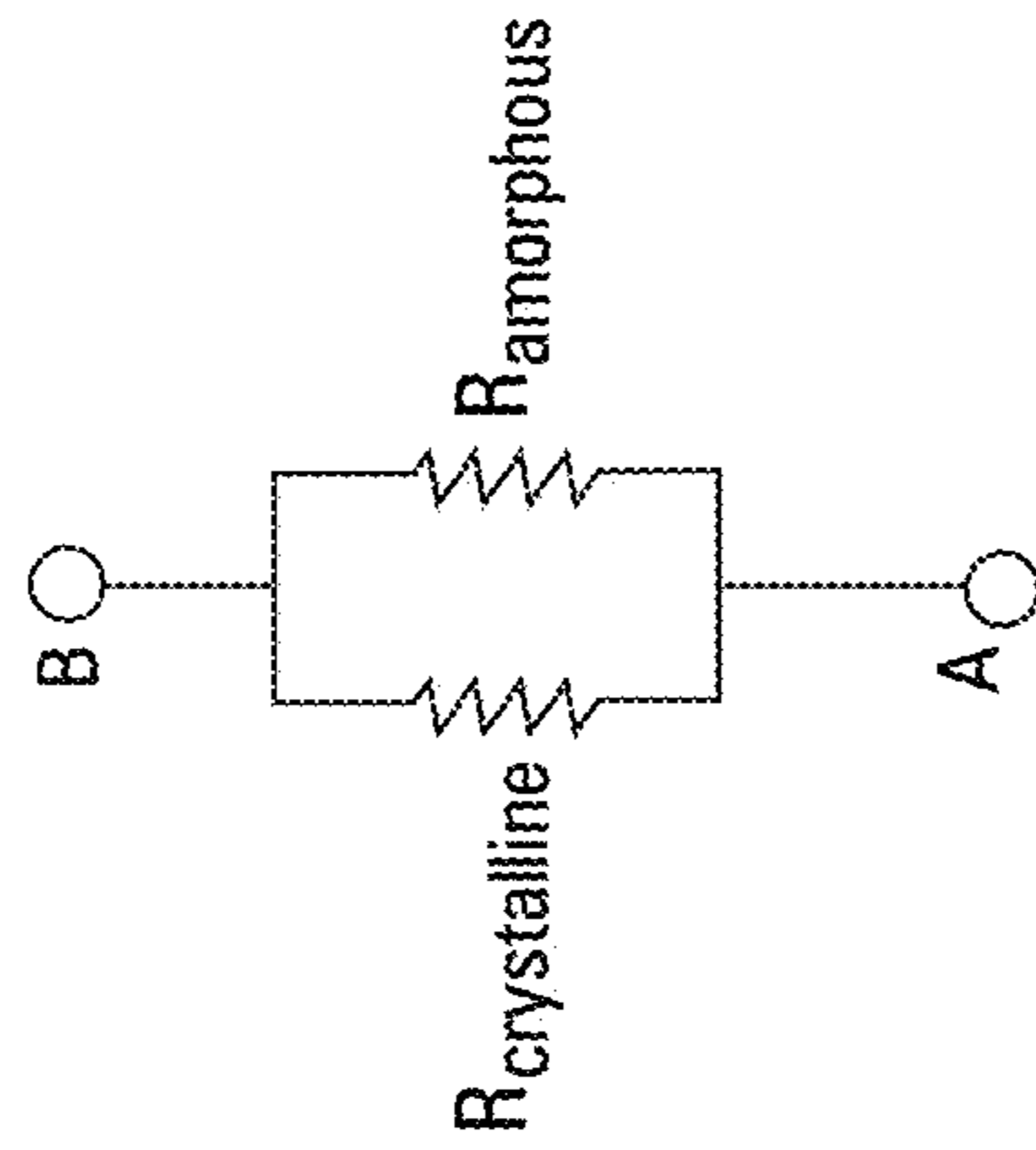
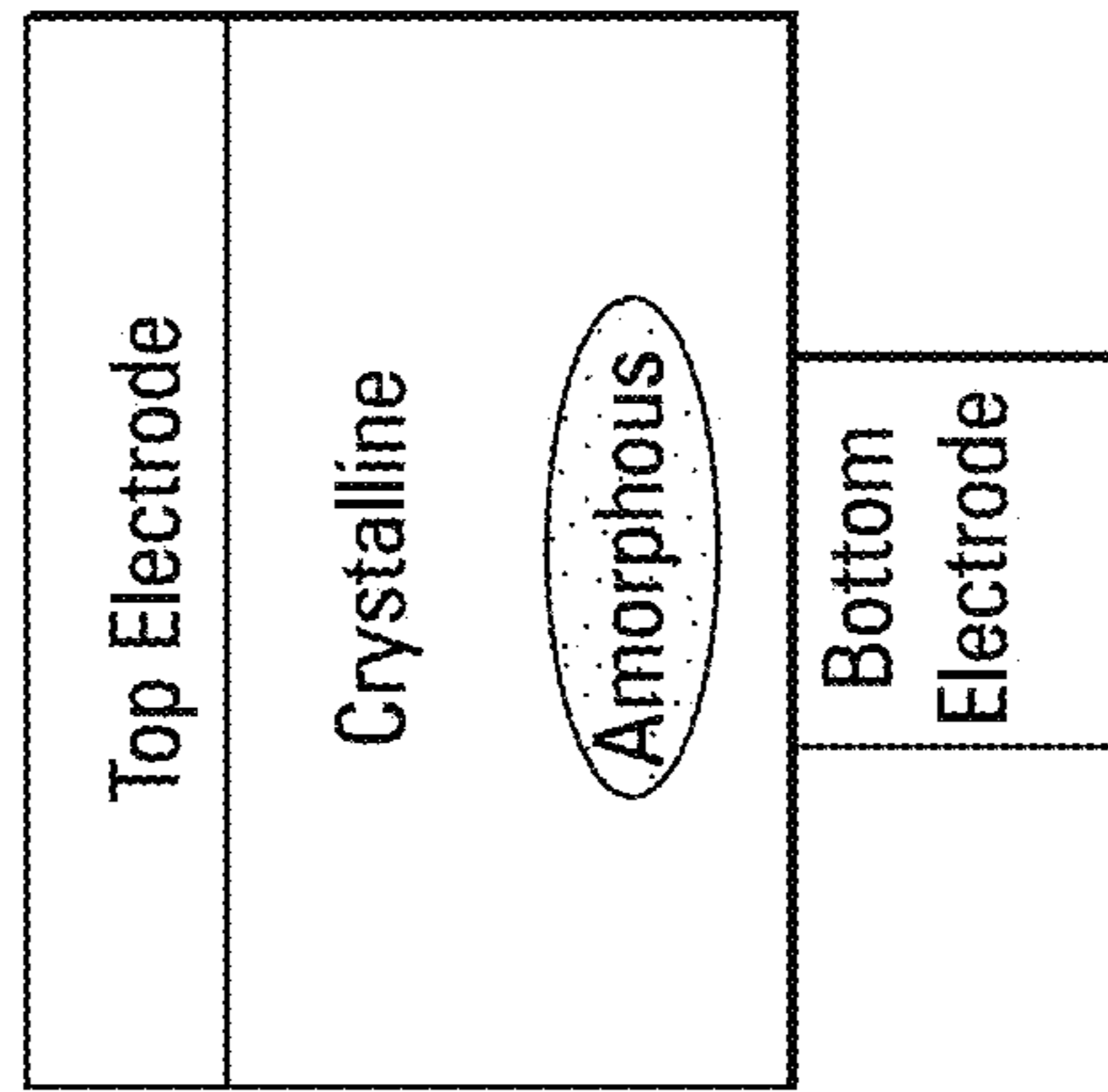


FIG. 4

FIG. 3

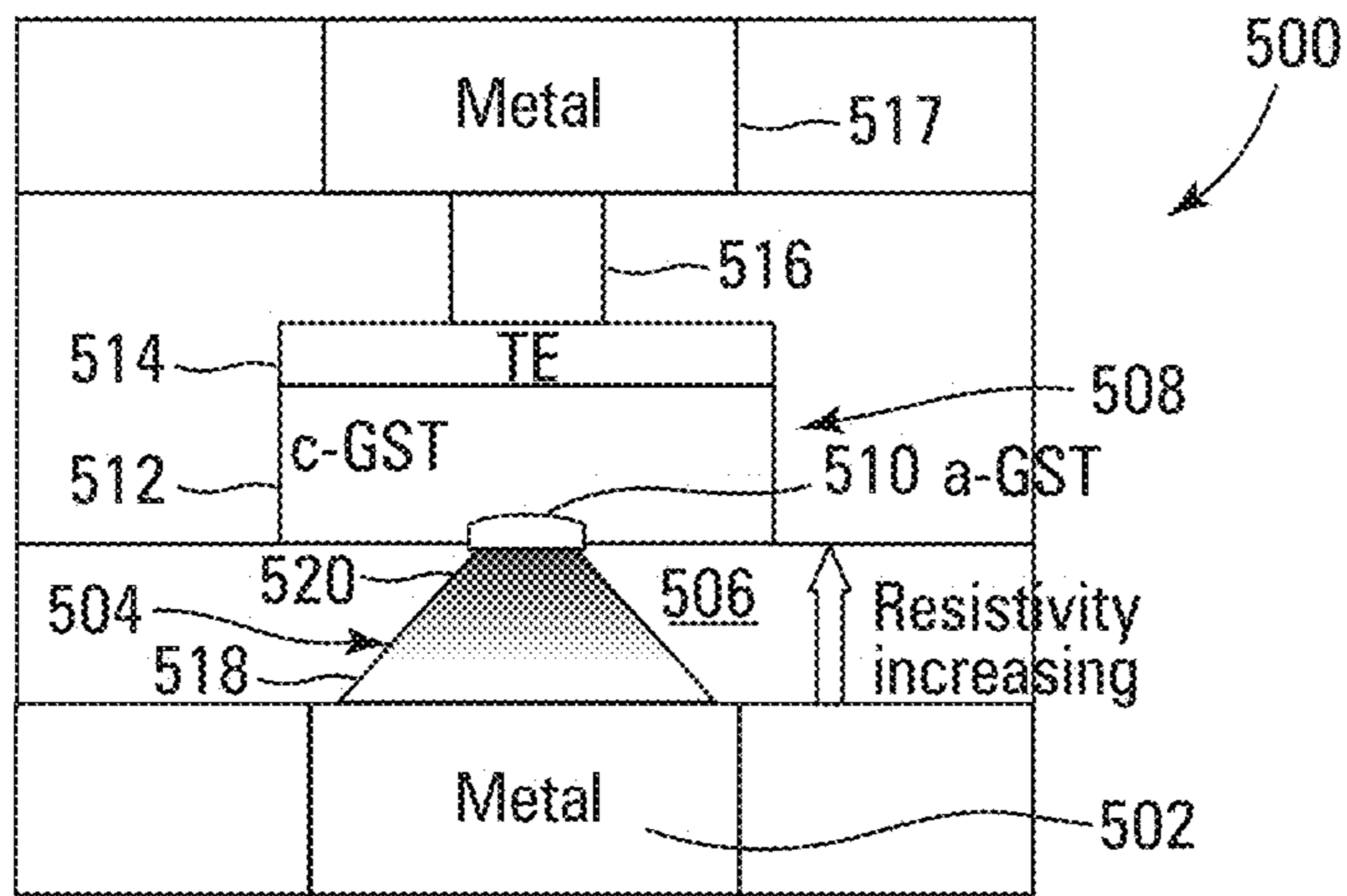


FIG. 5

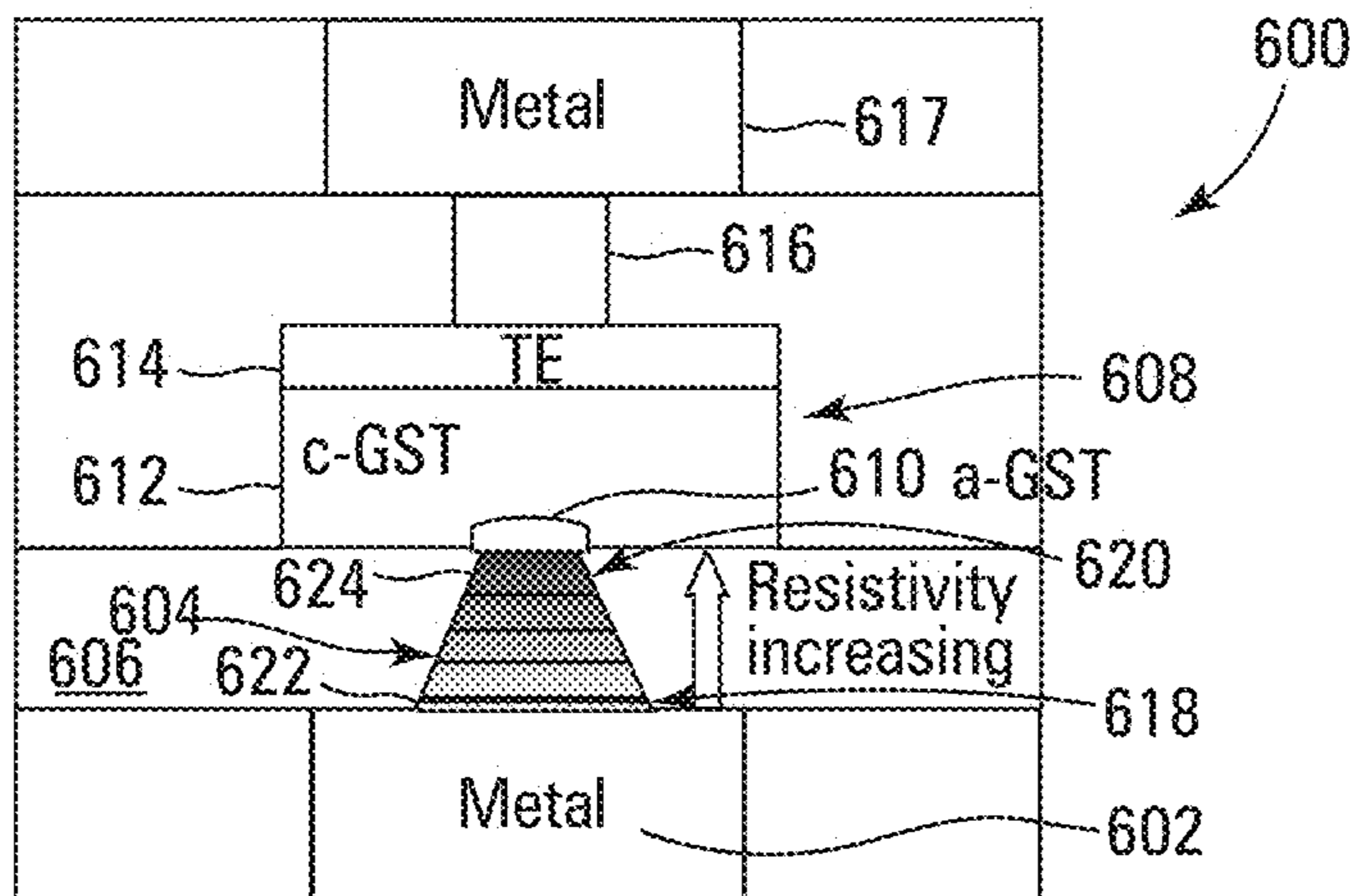


FIG. 6

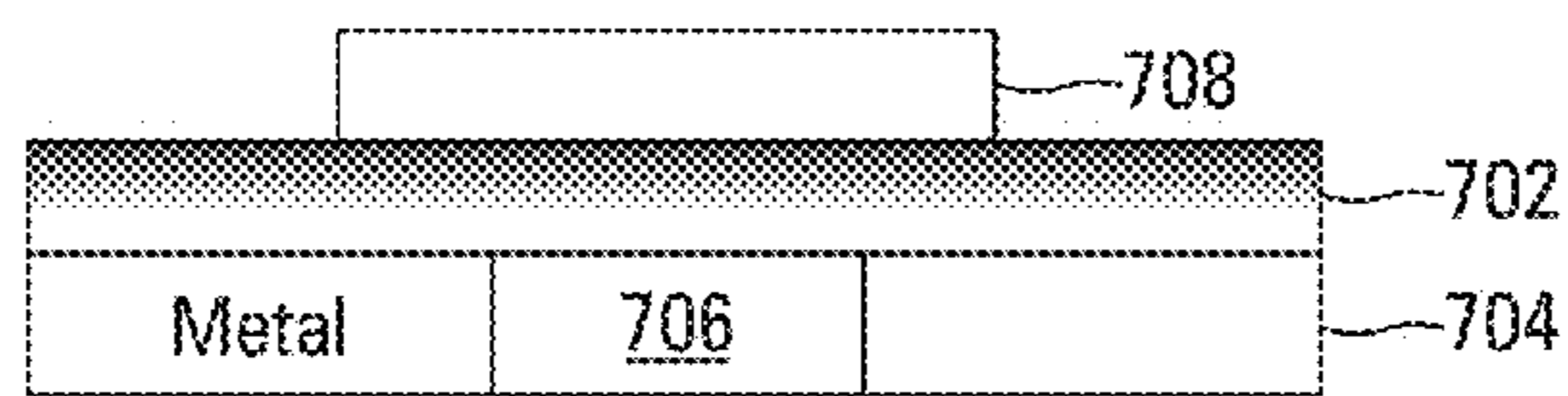


FIG. 7A

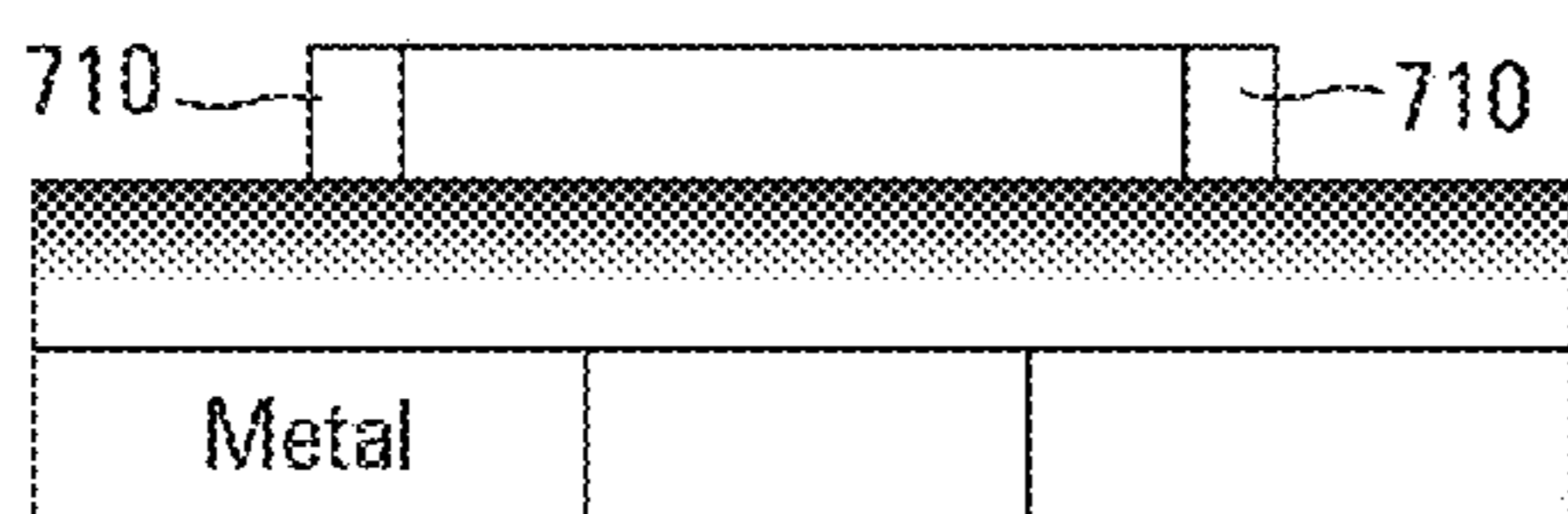


FIG. 7B

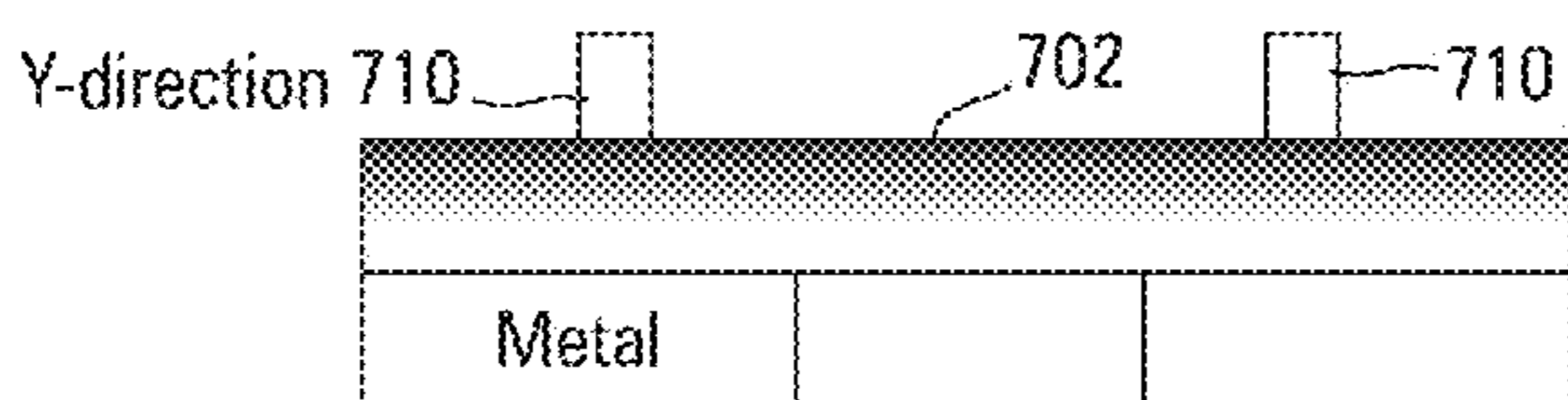


FIG. 7C

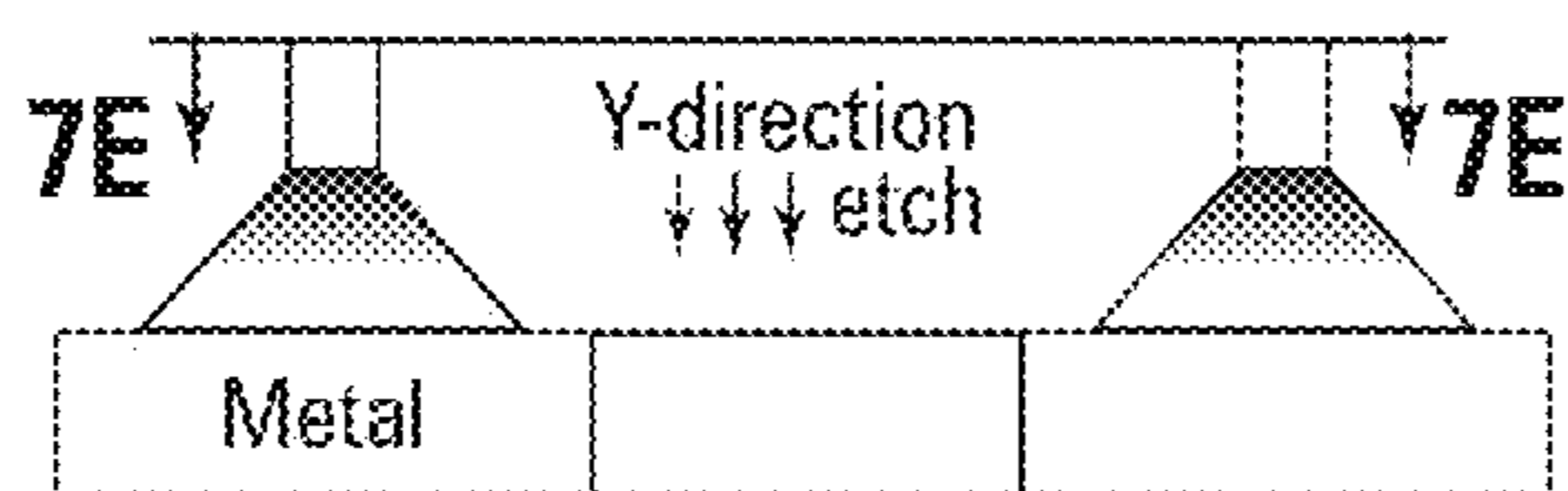


FIG. 7D

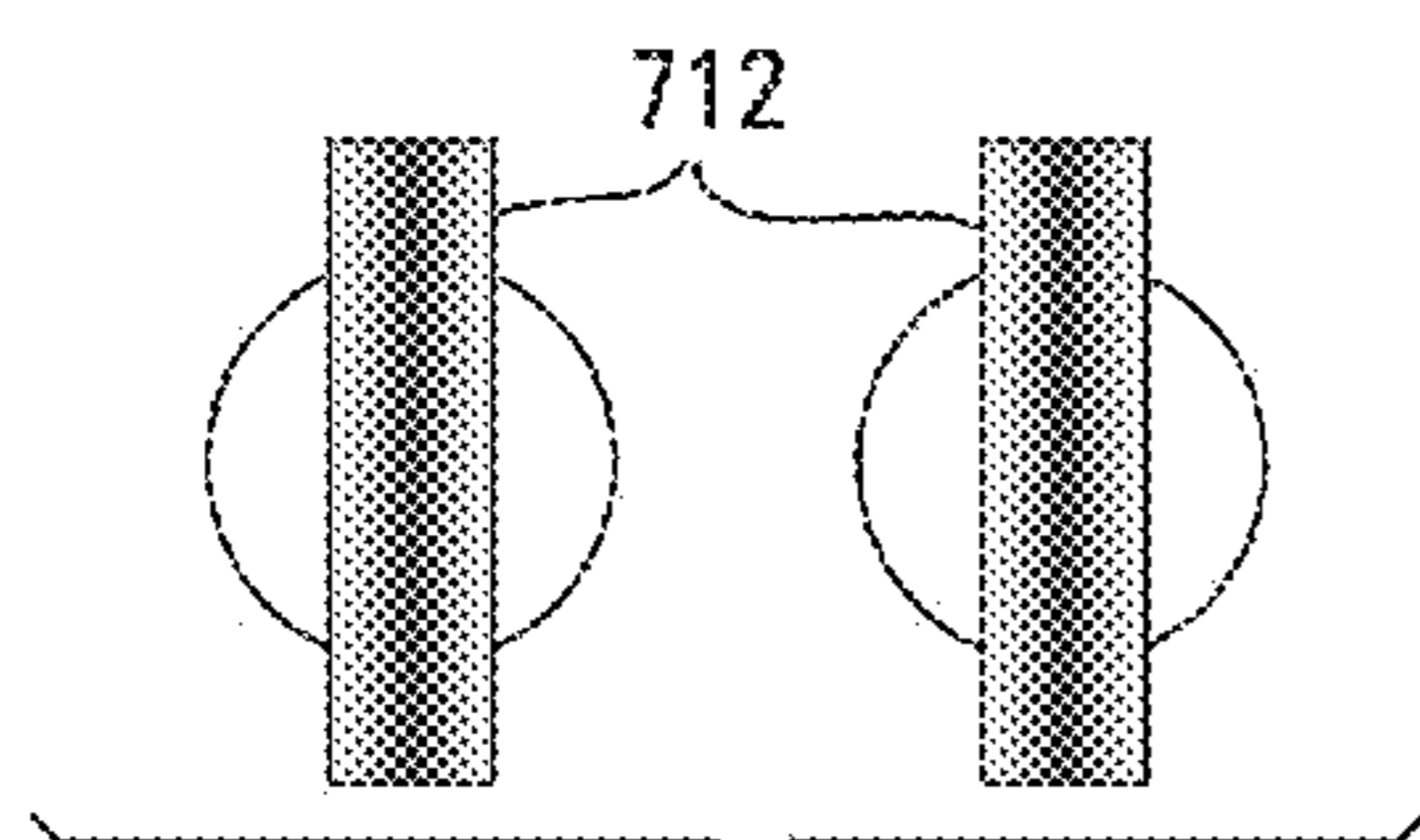


FIG. 7E

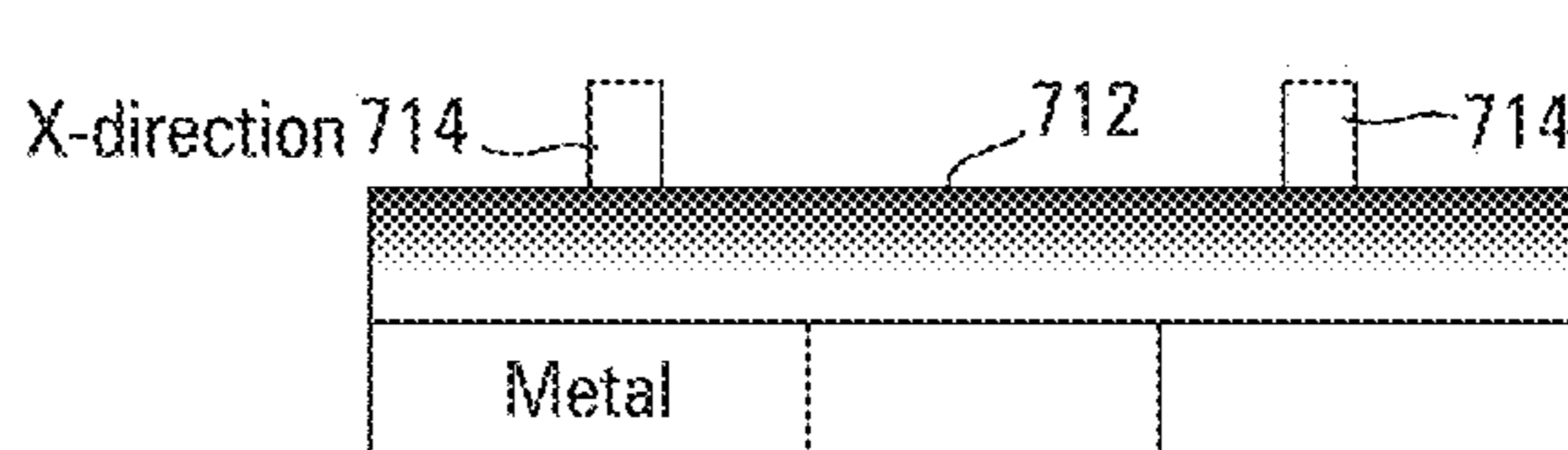


FIG. 7F

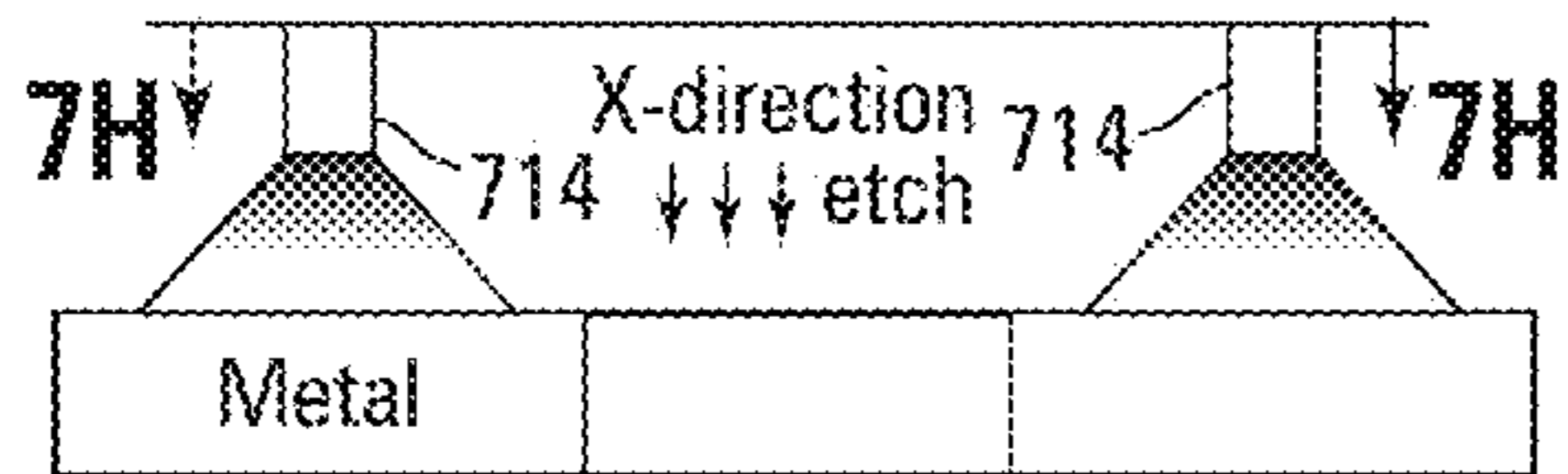


FIG. 7G

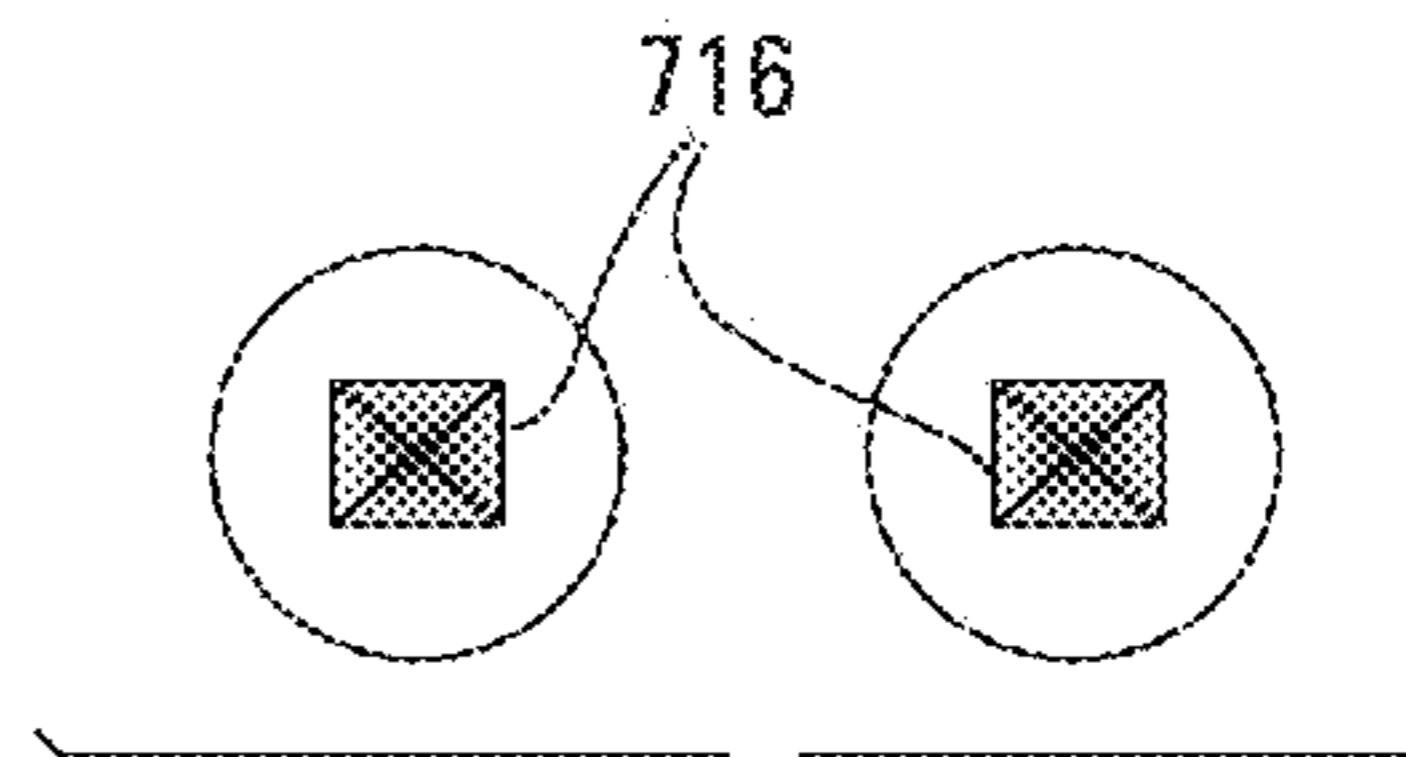


FIG. 7H

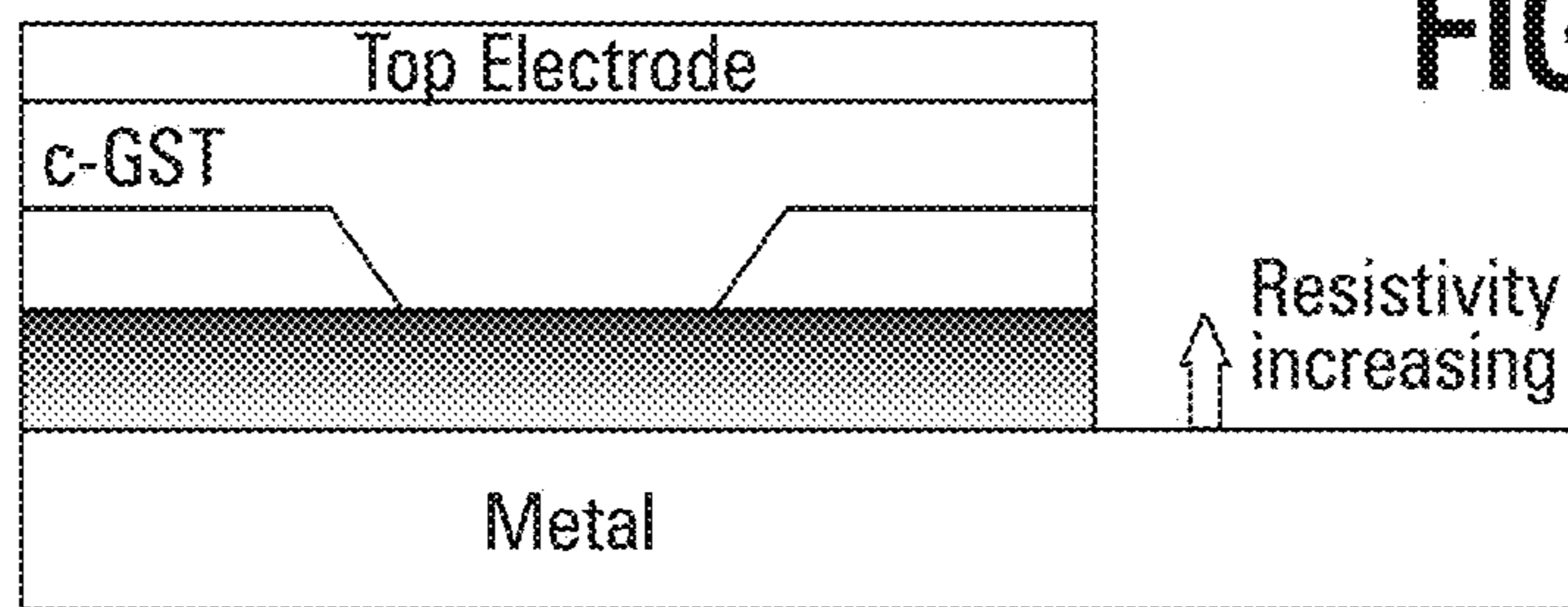


FIG. 8

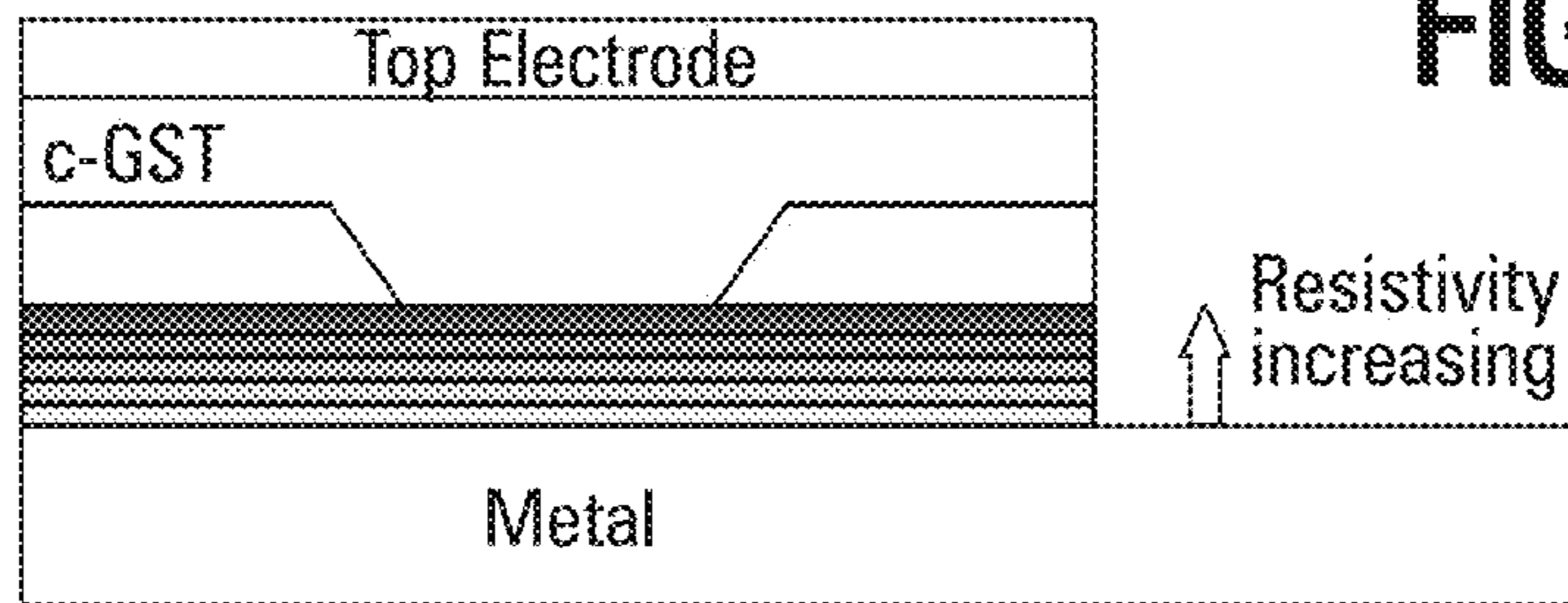


FIG. 9

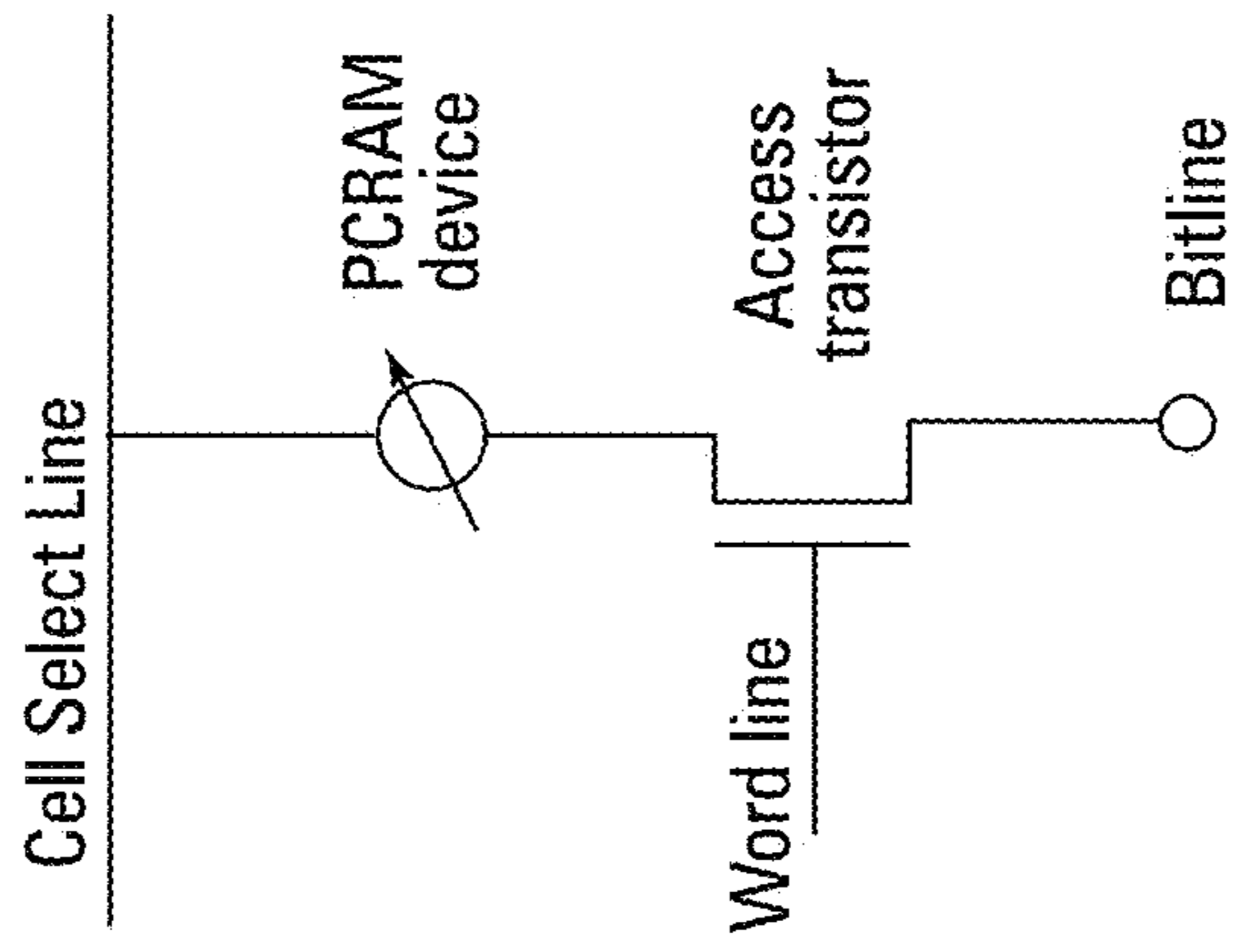
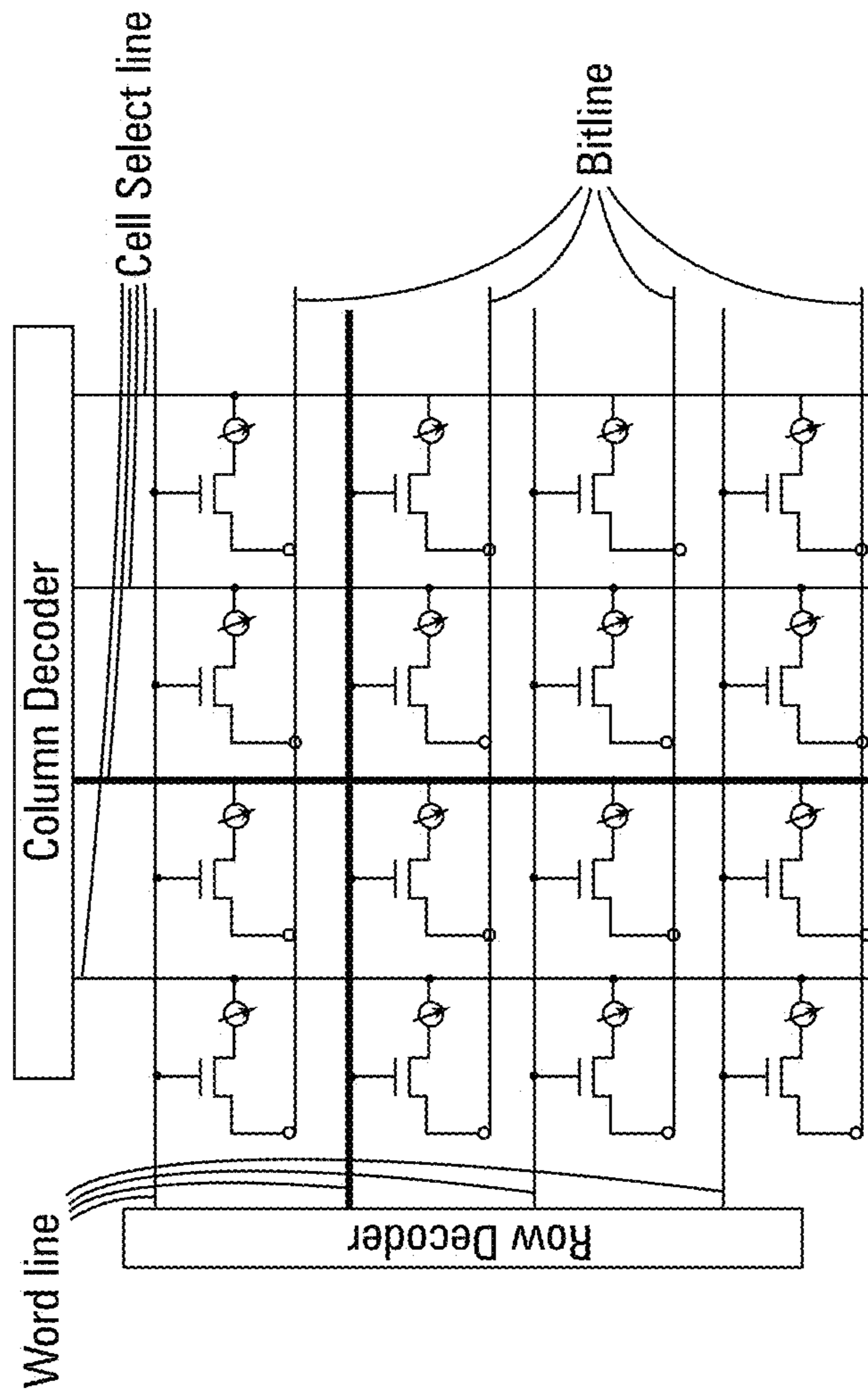


FIG. 10

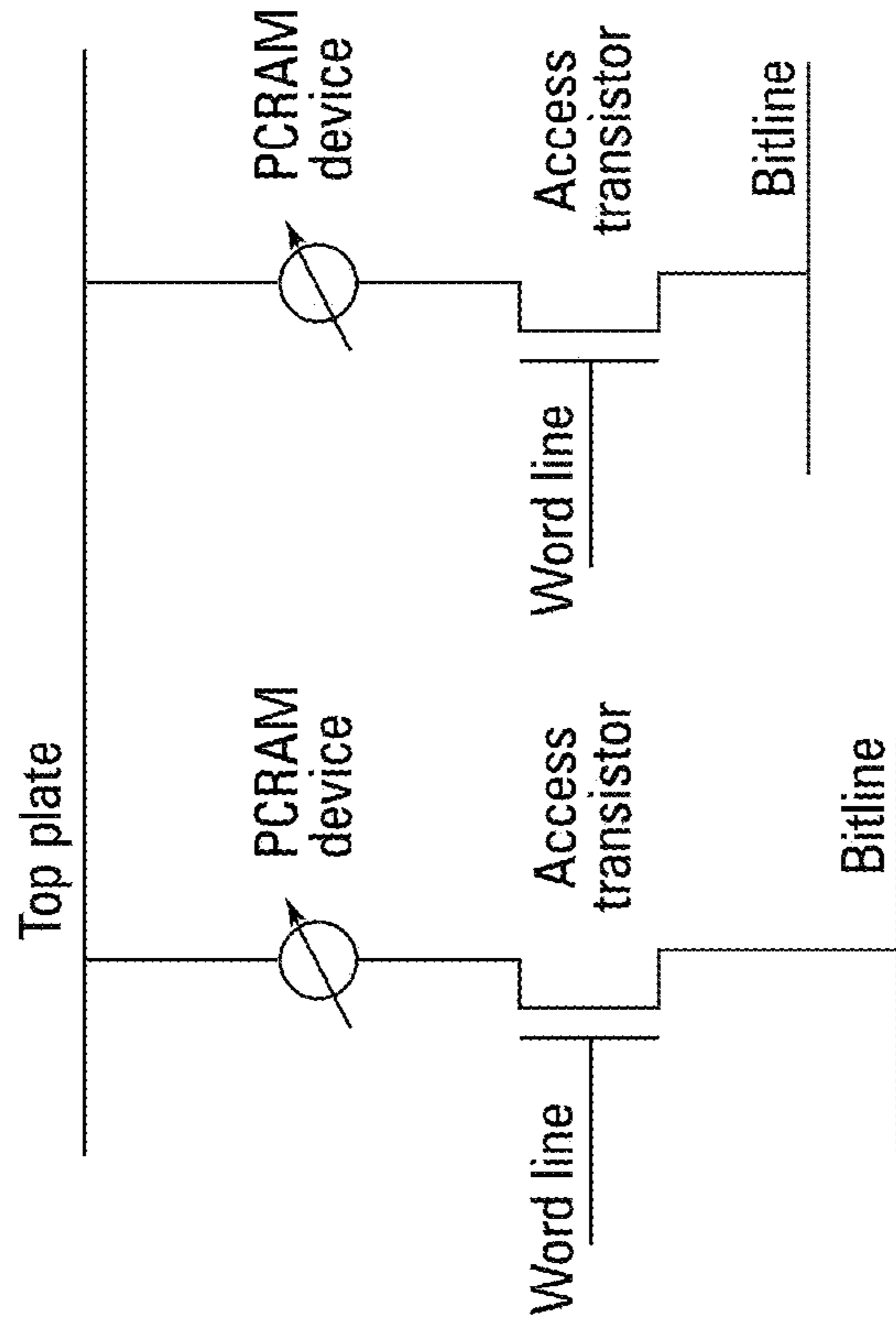
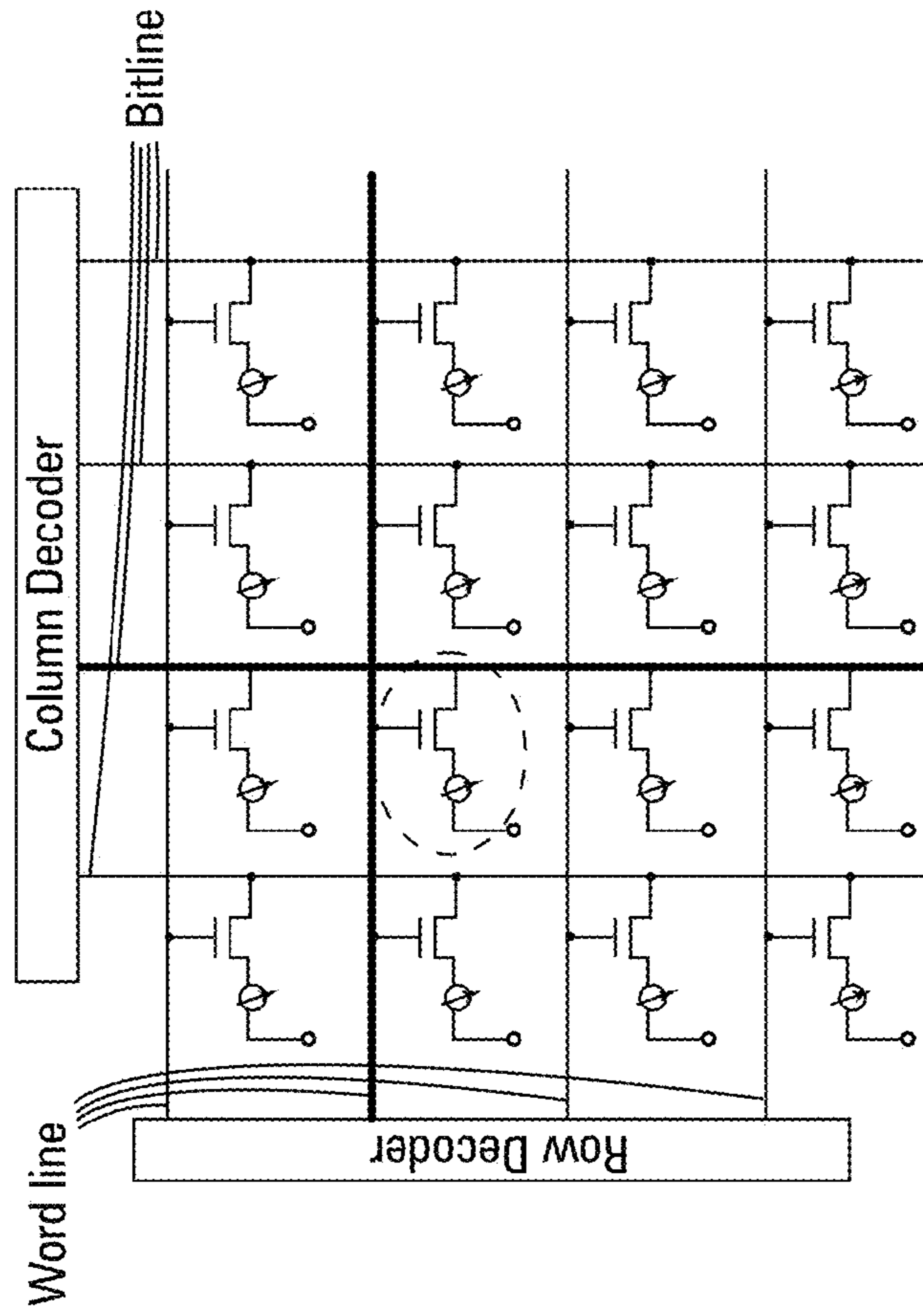


FIG. 11

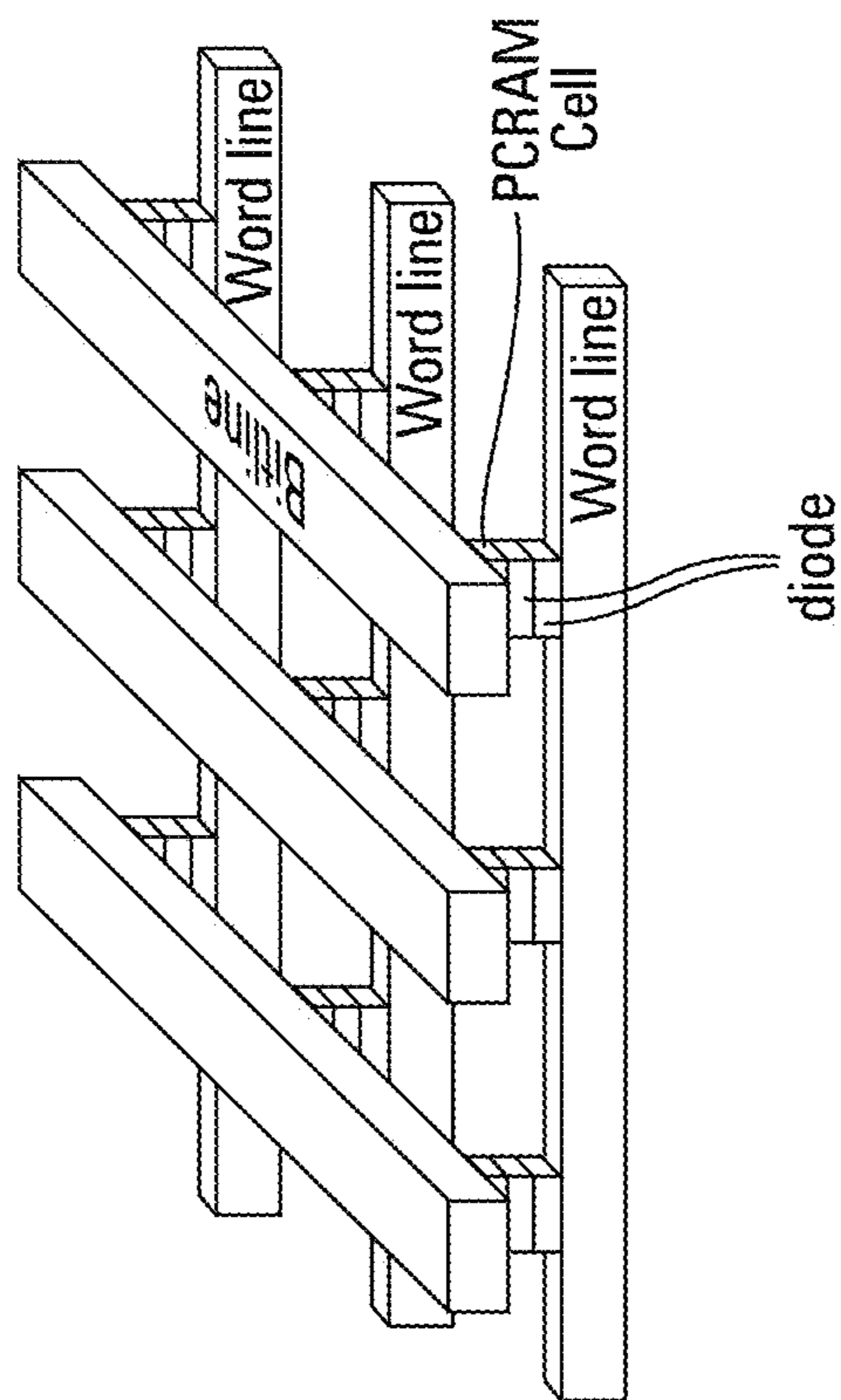
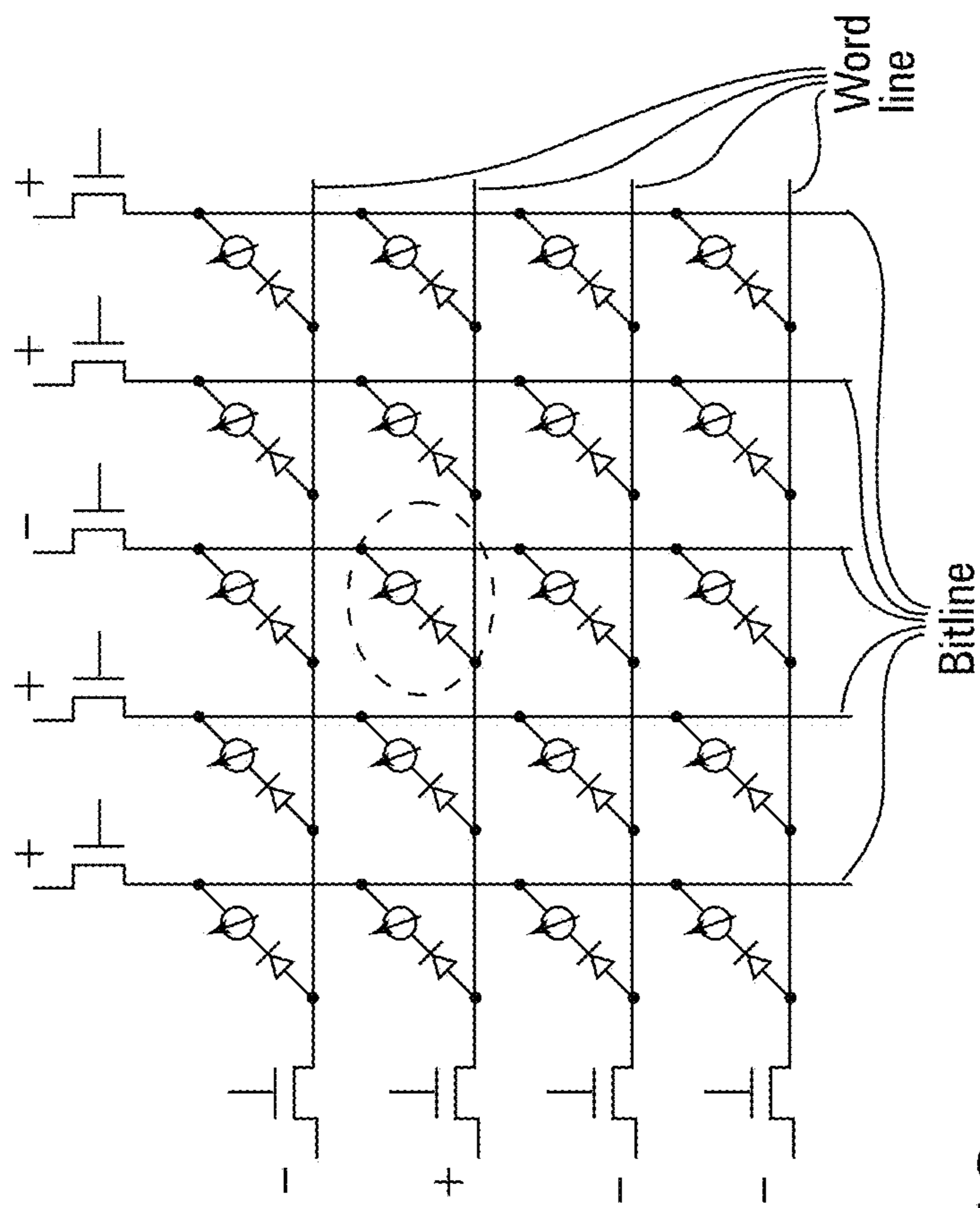


FIG. 12

MEMORY CELLS

RELATED APPLICATIONS

This Application is a Continuation of U.S. application Ser. No. 14/191,586, filed Feb. 27, 2014 (allowed), which is a Divisional of U.S. application Ser. No. 13/212,456, filed Aug. 18, 2011, now U.S. Pat. No. 8,679,934, issued on Mar. 25, 2014, which is a Divisional of U.S. application Ser. No. 11/512,858, filed Aug. 30, 2006, now U.S. Pat. No. 8,003,972, issued on Aug. 23, 2011 which are commonly assigned and incorporated herein by reference.

FIELD

The present disclosure relates generally to phase change memories and in particular the present disclosure relates to phase change memory electrodes.

BACKGROUND

Phase change random access memory (PCRAM) is a non-volatile form of memory that uses the reversible process of changing the state of an alloy containing one or more elements from Group V or VI of the periodic table between amorphous and crystalline states upon application of an electric current, and wherein the two states have substantially different electrical resistance. Typical current phase change memories use a chalcogenide alloy, such as a Germanium-Antimony-Tellurium (GeSbTe, or GST, most commonly $\text{Ge}_2\text{Sb}_2\text{Te}_5$) alloy. The amorphous (a-GST) and crystalline (c-GST) states of the material have largely different resistivity, on the order of three orders of magnitude, so that a determination of the state is easily done. The crystalline state has typical resistance on the order of kiloOhms ($\text{k}\Omega$), whereas the amorphous state has typical resistance on the order of megaOhms ($\text{M}\Omega$). The states are stable under normal conditions, so the PCRAM cell is a non-volatile cell with a long data retention. When the GST is in its amorphous state, it is said to be RESET. When the GST is in its crystalline state, it is said to be SET. A PCRAM cell is read by measuring its resistance.

The structure of a typical vertical PCRAM cell in a SET state **100** as shown in FIG. 1 includes a bottom metal contact **102**, a bottom electrode **104** surrounded by dielectric material **106**, a chalcogenide (GST) **108** having a crystalline portion (c-GST) **112**, a top electrode **114**, a metal top contact **116**, and a cell select line **118**. The GST **108** being all c-GST means that the GST has a high conductivity, and low resistance, typically on the order of $\text{k}\Omega$. The bottom electrode **104** is sometimes referred to as a heater.

A RESET structure of the PCRAM cell **100** is shown in FIG. 2. The bottom electrode **104** is typically a high conductivity, low resistivity metal or alloy (less than 1 milliOhms.cm ($\text{m}\Omega\cdot\text{cm}$)). To change the cell **100** from a SET state to a RESET state, a current is passed through the bottom metal contact **102** and bottom electrode **104**. This current heats a programmable volume region of the GST **108** near the top of the bottom electrode **104** to a temperature sufficient to melt the GST in that region. Typical melting points for many GST materials are in the range of 600 degrees C., although the melting point differs for other chalcogenides. When the current is removed, a section of the programmable volume of GST **108** that has been heated to its melting point rapidly cools due to heat dissipation into the surrounding materials. This rapid cooling does not allow the melted programmable

volume region to cool in a crystalline state. Instead, a region of amorphous GST (a-GST **110**) remains at or near the top of the heater **104**.

The desired a-GST region is a hemispherical region covering the top of the bottom electrode **104** and extending slightly into the field of c-GST. This allows for a high resistance of the GST **108**, as the resistances of the c-GST **112** and a-GST **110** portions behave electrically as series a connected resistance. This is shown in FIG. 3.

The majority of the heat generated by the current passing through the bottom electrode **104** does not contribute to heating of the GST **108**, since the heat is dissipated by the surrounding dielectric material **106**. Therefore, most of the heating of the programmable volume region of GST **108** is due to resistive heating near the top of the heater **106**.

In typical PCRAM cells, the cell (the GST layer) and the top electrode are patterned together with the current flowing from the top electrode contact to the bottom electrode. In this arrangement, current density is mostly symmetric. In an ideal RESET state, a hemispheric region of GST covering the entire area of the bottom electrode contact is converted to the amorphous state (a-GST **110**), to prevent a parallel leakage path.

The hottest region in the GST programmable volume is typically about 20 nanometers above the interface between the bottom electrode **104** and the GST **108** due to heat loss through bottom electrode **104**. The inefficient heating of low resistance bottom electrodes **104** combined with the hottest region being above the interface between the bottom electrode **104** and the GST **108** can create an amorphous GST region that is separated from the bottom electrode as shown in FIG. 4. This leads to a parallel resistance connection for the a-GST and c-GST regions, and the current flows through the low resistance path of the parallel circuit, the result being that the cell is stuck at a low resistance state and the GST cannot be converted back to a high resistance state.

Still further, a RESET current pulse that is too large will form an ideal hemispherical amorphous region covering the bottom electrode **104**, but will create a region of the GST that is too hot, often in excess of 900 degrees C. This hot spot can cause bubbling, sublimation, or composition change.

To switch the cell **100** from a RESET state to a SET state, a SET current is passed through the metal contact **102** and bottom electrode **104** to heat the a-GST section **110** near the top of the bottom electrode **104** to a temperature below the melting point, but sufficiently high (on the order of 350 degrees C. for typical GST materials, but different for other chalcogenides) at which the mobility of atoms in the region near the top of the bottom electrode **104** allows them to rearrange from an amorphous state to a crystalline state. The resulting configuration has a GST **108** that is all crystalline, as is shown in FIG. 1.

The currents used to SET and RESET the cell are typically as follows. A SET state is achieved by applying a voltage or current pulse sufficient to raise the GST temperature in the programmable volume to below the melting point but above its crystallization temperature, and is held for a sufficient time to allow the rearranging of the atoms to a crystalline state. A RESET state is achieved by applying a voltage or current pulse sufficient to raise the GST temperature in the programmable volume to the melting point, and is held typically for a shorter time than the SET pulse. The SET pulse is typically longer in duration but of lower amplitude than the RESET pulse. The RESET pulse is typically shorter in duration but of higher amplitude than the SET pulse. The actual amplitudes and durations of the pulses depend upon the size of the cells and the particular phase change materials used in the cell.

RESET currents for many GST cells are currently in the 400 to 600 microAmpere (μA) range, and have durations in the 10-50 nanosecond range, whereas SET currents are currently in the 100 to 200 μA range and have durations in the 50-100 nanosecond range. Read currents are lower than either SET or RESET currents. As cell size continues to decrease, the currents involved and the durations thereof also continue to decrease.

For the reasons stated above, and for other reasons stated below which will become apparent to those skilled in the art upon reading and understanding the present specification, there is a need in the art for improved PCRAM structures and methods for phase change memory switching.

BRIEF DESCRIPTION OF DRAWINGS

FIG. 1 is a cross-sectional view of a typical phase change memory cell in a SET state;

FIG. 2 is a cross-sectional view of a typical phase change memory cell in a RESET state;

FIG. 3 is a partial cross-sectional view of a desired RESET structure in a phase change memory cell;

FIG. 4 is a partial cross-sectional view of a failure state RESET structure in a phase change memory cell;

FIG. 5 is a cross-sectional view of a vertical phase change memory cell according to one embodiment;

FIG. 6 is a cross-sectional view of a vertical phase change memory cell according to another embodiment;

FIGS. 7A to 7H are in-process cross-sectional views of formation of a phase change memory cell according to another embodiment;

FIG. 8 is a cross-sectional view of a cell-in-the-via phase change memory cell according to one embodiment;

FIG. 9 is a cross-sectional view of a cell-in-the-via phase change memory cell according to another embodiment;

FIG. 10 is a simplified circuit diagram of a portion of a memory array according to another embodiment;

FIG. 11 is a simplified circuit diagram of a portion of a memory array according to another embodiment; and

FIG. 12 is a simplified circuit diagram of a portion of a memory array according to another embodiment.

DETAILED DESCRIPTION

In the following detailed description of the embodiments, reference is made to the accompanying drawings that form a part hereof. In the drawings, like numerals describe substantially similar components throughout the several views. These embodiments are described in sufficient detail to enable those skilled in the art to practice the embodiments. Other embodiments may be utilized and structural, logical, and electrical changes may be made without departing from the scope of the application.

The following detailed description is, therefore, not to be taken in a limiting sense, and the scope of the present disclosure is defined only by the appended claims, along with the full scope of equivalents to which such claims are entitled.

Plug bottom electrodes of PCRAM cells are often of a shape that slopes from the bottom of the bottom electrode toward the top, with the electrode having a larger cross-sectional area at the top of the bottom electrode near the interface between the bottom electrode and the phase change material than at the bottom of the bottom electrode. This further contributes to inefficiency because for the same current through the plug, a larger cross-sectional area provides even less resistive heating than a smaller cross-sectional area. The current being equal, the resistance of the material at the

lower part of the bottom electrode is higher, which generates more heat than the upper portion. This heat is quickly dissipated into the surrounding dielectric and does not contribute to heating of the programmable volume of the phase change material.

Embodiments disclosed herein use a graded or layered resistivity bottom electrode of a PCRAM cell to increase the contribution of the bottom electrode to heating of a programmable region of a phase change material of the cell. Still further, the bottom electrode is patterned as a conical-like shape with smaller cross sectional area at the interface between the bottom electrode and the GST of the PCRAM cell. While GST is used in the description herein, it should be understood that other phase change materials including other chalcogenides, are amenable to use with the various embodiments. For example only, phase change materials include but are not limited to GeTe, In—Se, Sb_2Te_3 , GaSb, InSb, As—Te, Al—Te, Ge—Sb—Te, Te—Ge—As, In—Sb—Te, Te—Sn—Se, Ge—Se—Ga, Bi—Se—Sb, Ga—Se—Te, Sn—Sb—Te, In—Sb—Ge, Te—Ge—Sb—S, Te—Ge—Sn—O, Te—Ge—Sn—Au, Pd—Te—Ge—Sn, In—Se—Ti—Co, Ge—Sb—Te—Pd, Ge—Sb—Te—Co, Sb—Te—Bi—Se, Ag—In—Sb—Te, Ge—Sb—Se—Te, Ge—Sn—Sb—Te, Ge—Te—Sn—Ni, Ge—Te—Sn—Pd, Ge—Te—Sn—Pt, and the like. For purposes of this application, resistivity refers to electrical resistivity.

FIG. 5 shows a vertical PCRAM cell 500 in cross section. Cell 500 includes a mostly typical set of components similar to those shown in FIGS. 1 and 2, and operates under the same general principles. A lower metal contact 502 has thereon a bottom electrode 504 surrounded by dielectric material 506. A phase change material 508, such as a chalcogenide or GST material, is above the bottom electrode 504, and is topped with a top electrode 514, a top metal contact 516, and a cell select line 517. The phase change material 508 is shown in FIG. 5 having an amorphous region 510 and a crystalline region 512. The bottom electrode 504 has a tapered cross section, and a resistivity gradient from its bottom 518 toward its top 520. The resistivity of the bottom electrode 504 increases from a lower resistivity at bottom 518 to a high resistivity at top 520.

The bottom electrode 504 is shown as tapered in FIG. 5, but it should be understood that an increasing resistivity bottom electrode without the conical-like shape also provides an increased amount of heat at the interface between the bottom electrode 504 and the phase change material 508. This is because the smallest cross-sectional area and the highest resistivity of the bottom electrode is closest to the programmable volume of the phase change cell material. The lower resistivity of the lower portion of the bottom electrode reduces heat loss to the surrounding dielectric 506, and reduces the likelihood of parasitic series resistance from the bottom electrode 504.

FIG. 6 shows another vertical PCRAM cell 600 in cross section. Cell 600 includes a mostly typical set of components similar to those shown in FIGS. 1 and 2, and operates under the same general principles. A lower metal contact 602 has thereon a bottom electrode 604 surrounded by dielectric material 606. A phase change material 608, such as a chalcogenide or GST material, is above the bottom electrode 604, and is topped with a top electrode 614, a top metal contact 616, and a cell select line 617. The phase change material 608 is shown in FIG. 6 having an amorphous region 610 and a crystalline region 612. The bottom electrode 604 has a tapered cross section, and a plurality of layers of material having increasing resistivity, with the lowest resistivity layer

622 at the bottom **618** of the bottom electrode **604** and the highest resistivity layer **624** at the top **620** of bottom electrode **604**.

The bottom electrode **604** is shown as tapered in FIG. 6, but it should be understood that increasing resistivity layers of the bottom electrode without the conical-like shape also provides an increased amount of heat at the interface between the bottom electrode **604** and the phase change material **608**. This is because the smallest cross-sectional area and the highest resistivity layer of the bottom electrode is closest to the programmable volume of the phase change cell material. The lower resistivity of the lower layers of the bottom electrode reduces heat loss to the surrounding dielectric **606**, and reduces the likelihood of parasitic series resistance from the bottom electrode **604**.

One problem with simply making the entire heater a high resistivity material is that partial heating of the cell GST will occur, but a majority of the heat generated by the current passing through the high resistivity heater will be dissipated into the surrounding dielectric without contributing to the heating of the GST material. Further, power consumption will increase due to the high amounts of voltage required to get current to the GST region through the high resistivity heater element.

The bottom electrode **504** is in various embodiments formed of a substance that can easily be given a resistively gradient during formation, for example, TiN, ZrN, HfN, VN, NbN, TaN, TiAlN, TaSiN, TiCN, and the like. Resistivity of materials such as TiN, ZrN, HfN, VN, NbN, TaN, TiAlN, TaSiN, TiCN, and the like can be increased by a few orders of magnitude during deposition by increasing the concentration of Nitrogen. This increase in Nitrogen concentration can be accomplished, for example, by adjusting Nitrogen-containing gas ratio during chemical vapor deposition or physical vapor deposition of the bottom electrode material or low energy Nitrogen plasma source implantation. Examples of resistivity differences between the bottom of the bottom electrode and the top of the bottom electrode are for example, less than 1 milliOhm.cm at the bottom to upwards of 6 or more milliOhm.cm at higher Nitrogen concentrations. The bottom electrode **604** is in various embodiments formed in layers of increasing resistivity.

The high resistivity material close to the GST programmable volume creates a partial heating of the GST programmable volume by the resistive heating at the electrode tops **520** and **620**. This heating serves to move the hottest region of the GST closer to the interface between the bottom electrodes **504** and **604** and the GST **508** and **608**, and to prevent the formation of an amorphous region of GST separated from the tops of the bottom electrodes **504** and **604**. It also helps to reduce the programming current requirement of phase change memory cells.

The embodiments herein concentrate heating due to the bottom electrodes **504** and **604** at their tops where the high resistivity material is, that is, near the interface between the bottom electrodes **504** or **604** and the GST **508** or **608**. The heat produced by the high resistivity material at the tops of bottom electrodes **504** and **604** is close to the cell interface, and provides efficient heating of the programmable volume, and prevents the formation of a crystalline GST region between the bottom electrodes **504**, **604** and the amorphous GST region formed at the tops of the bottom electrodes **504**, **604**. Further, since high electrical resistivity material has a lower thermal conductivity than low electrical resistivity material, the traditional heat sink effect of a low electrical resistivity heater element is reduced at or near the interface

between the heater element and the GST. In combination, the programming current requirements can also be reduced.

A bottom electrode according to one embodiment includes an electrode that tapers from its largest cross-sectional area to its smallest cross-sectional area between a bottom metal contact and the phase change cell material. As the cross-sectional area decreases, reaching its smallest area at the interface between the bottom electrode and the phase change cell material, with an equal current, the opposite effect of traditional bottom electrodes occurs. For the same current, the resistance of the bottom electrode is at its highest at the interface between the bottom electrode and the phase change cell material. Therefore, the top of the bottom electrode, closest to the phase change material, generates more heat than the lower portion of the electrode.

In another embodiment, a graded resistivity material is used for forming the bottom electrode. The resistivity of the bottom electrode is increased the closer the portion of the electrode is to the interface between the bottom electrode and the phase change cell material. That is, the resistivity increases from the bottom of the bottom electrode toward the top of the bottom electrode. The increased resistivity provides a higher heat concentration at the top of the electrode, where it is most able to provide heat to the programmable volume of the phase change cell material. Gradation of material is accomplished through known deposition techniques for increasing concentration of dopants in a material during deposition, for example.

In another embodiment, instead of a bottom electrode with a resistivity gradient, a series of layers of increasing resistivity are deposited, the lowest resistivity material being in the lowest layer of the bottom electrode, with increasing resistivity layers toward the top of the bottom electrode. The highest resistivity layer is at the top of the bottom electrode, where it contributes the most toward heating the programmable volume of the phase change material at the interface between the bottom electrode and the phase change cell material.

In other embodiments, a graded resistivity bottom electrode or a layered resistivity electrode such as those described above are combined with a tapered bottom electrode, also as described above. This provides a tapered bottom electrode having a smaller cross-sectional area at the top of the bottom electrode versus the bottom of the bottom electrode, as well as graded or layered resistivity, which further increases the heating close to the phase change cell material, and reduces heat loss to surrounding dielectrics in the lower portions of the bottom electrode.

The bottom electrodes **504** and **604** described above can be formed in a number of ways. FIGS. 7A to 7H show the formation of an electrode such as electrode **504** in a series of in-process cross-sectional views. During formation of the PCRAM cell **500**, a layer of bottom electrode material **702** is deposited over metal contacts and substrate **704** and **706**, followed by, for example, a photoresist layer **708** or a sacrificial dielectric layer. Spacers **710** are deposited using, for example, a chemical vapor deposition process, and are shown in FIG. 7B. The spacers **710** are aligned in the Y direction, and following appropriate etching to remove layer **708**, the spacers **710** remain, and are centered over the metal contacts **704** in the Y direction as shown in FIG. 7C. The spacers can be made to sizes smaller than current lithography techniques will allow, with dimensions of 20 nanometers or smaller. Using an etch, such as a reactive ion etching process, as shown in the Y directions in FIG. 7D, bottom electrode material **712** remains, in a structure tapered along the Y direction, as shown in FIG. 7E. The spacers **710** are removed. Next, spacers **714** are deposited in similar fashion as spacers

710 described above, but in the X direction as is shown in FIG. 7F. Using another etch, as shown in the X direction in FIG. 7G, bottom electrodes 716 (like bottom electrodes 504 and 604) remain, and the sacrificial spacers are subsequently removed. The bottom electrodes 716 are shown in top view in FIG. 7H with a tapered shape smaller at their tops and larger at their bottoms. Etching to allow tapered structures is accomplished in a variety of ways, including angling the ion source to create tapered structures, and the like, and will not be described further herein. Following the formation of the cone-like bottom electrodes 716, dielectric is deposited between the electrodes and the structure is planarized, followed by deposition of the GST phase change layer and top metal contacts.

Formation of the PCRAM cell using a layered resistivity bottom electrode such as cell 604 is performed in much the same method as the formation of cell 500, except using a plurality of layers if increasing resistivity bottom electrode material as opposed to a graded resistivity bottom electrode material.

The various embodiments have been shown with vertical PCRAM cells. The layered or graded resistivity electrodes are also provided with cell-in-the-via PCRAM cells, such as those shown in FIGS. 8 and 9. Cell-in-the-via structures have a bottom electrode larger than the GST cell size. A resistivity gradient or layered resistivity layers with increasing resistivity near the top of the bottom electrode provides increased heating at the interface between the bottom electrode and the phase change cell material.

PCRAM memory arrays can take several different forms, each of which are amenable to use with the bottom electrode cap configuration PCRAM cells described above. Examples of PCRAM memory arrays include an array of PCRAM cells each comprising an access transistor (metal oxide semiconductor field effect transistor (MOSFET) or bipolar transistor) and one PCRAM cell, in other words a 1T1C configuration. The resistance of the PCRAM cell can be switched between high and low states by resetting the GST of the cell to an amorphous state (high resistance) or setting the cell to a crystalline state (low resistance). Both set and reset currents are provided through the access transistor. An example of a portion of a PCRAM array of this type is shown in FIG. 10. A cell is selected by selecting its corresponding word line and cell select line. Bitlines may be tied to a common voltage source or individually selected. To RESET a cell, a large short pulse is applied to the corresponding cell select line while its word line is turned on. The RESET current flows through the selected memory element and resets the cell. To SET a cell, a smaller but longer pulse is applied to the cell select line to heat the memory element above its crystallization temperature but below its melting point. To read a cell, a voltage smaller than the threshold switching voltage of amorphous phase change material is applied to the cell select line.

Another PCRAM memory array uses a large block of phase change material and a top electrode, and is shown in general in FIG. 11. A common voltage is applied to the top electrode to bias all memory bits. A memory element is selected by selecting its word line and bitline.

Yet another PCRAM memory array is shown in FIG. 12. Diode-accessed cross-point PCRAM arrays select a memory element by biasing its word line high and non-selected word lines low, while biasing its selected bitline low and non-selected bitlines high. Only the diode connected to the selected cell is forward biased. All other diodes are reverse biased or do not have sufficient bias to overcome their threshold voltage, and no current flows except in the selected cell.

PCRAM arrays can be used in various memory devices, and may be coupled to a processor or memory controller, and may form part of an electronic system, including but not limited to memory modules for computers, cameras, portable storage devices, digital recording and playback devices, PDAs, and the like.

CONCLUSION

PCRAM cells and methods of forming them have been described that include tapered and untapered graded resistivity bottom electrodes; and tapered or untapered layered resistivity bottom electrodes, to provide localized heating of a GST layer of the cell, preventing separation of an amorphous GST region from the top of the bottom electrode. Tapered and untapered electrodes are provided in vertical PCRAM cells. Untapered electrodes are provided in cell-in-the-via PCRAM cells. Further, programming current requirements are reduced.

Although specific embodiments have been illustrated and described herein, it will be appreciated by those of ordinary skill in the art that any arrangement, which is calculated to achieve the same purpose, may be substituted for the specific embodiments shown. This application is intended to cover any adaptations or variations of the embodiments. Therefore, it is manifestly intended that this application be limited only by the claims and the equivalents thereof.

What is claimed is:

1. A memory cell, comprising:

- a first electrode having a surface;
 - a second electrode having a surface facing the surface of the first electrode; and
 - a phase change material between the first electrode and the second electrode and having a surface facing the surface of the second electrode;
- wherein the second electrode comprises a plurality of portions of material, each portion having a respective distance from the surface of the phase change material and each portion having a respective resistivity;
- wherein a portion of the plurality of portions of material farthest from the surface of the phase change material has a lowest resistivity of the plurality of portions of material and a portion of the plurality of portions of material closest to the surface of the phase change material has a highest resistivity of the plurality of portions of material; and
- wherein the resistivity of each individual portion is lower than the resistivity of each portion located closer to the surface of the phase change material, and higher than the resistivity of each portion located farther from the surface of the phase change material.

2. The memory cell of claim 1, wherein the phase change material is selected from a group consisting of GeTe, In—Se, Sb₂Te₃, GaSb, InSb, As—Te, Al—Te, Ge—Sb—Te, Te—Ge—As, In—Sb—Te, Te—Sn—Se, Ge—Se—Ga, Bi—Se—Sb, Ga—Se—Te, Sn—Sb—Te, In—Sb—Ge, Te—Ge—Sb—S, Te—Ge—Sn—O, Te—Ge—Sn—Au, Pd—Te—Ge—Sn, In—Se—Ti—Co, Ge—Sb—Te—Pd, Ge—Sb—Te—Co, Sb—Te—Bi—Se, Ag—In—Sb—Te, Ge—Sb—Se—Te, Ge—Sn—Sb—Te, Ge—Te—Sn—Ni, Ge—Te—Sn—Pd, and Ge—Te—Sn—Pt.

3. The memory cell of claim 1, wherein a thermal conductivity of each individual portion is higher than a respective thermal conductivity of each portion located closer to the surface of the phase change material, and lower than a respective thermal conductivity of each portion located farther from the surface of the phase change material.

4. The memory cell of claim 1, wherein the resistivity of the portion of the plurality of portions of material farthest from the surface of the phase change material is less than one milliOhm.cm and the resistivity of the portion of the plurality of portions of material closest to the surface of the phase change material is equal to or greater than six milliOhm.cm.

5. The memory cell of claim 1, wherein the plurality of portions of material each comprise a particular material selected from a group consisting of TiN, ZrN, HfN, VN, NbN, TaN, TiAlN, TaSiN, and TiCN.

6. The memory cell of claim 5, wherein a nitrogen content of each individual portion is lower than a respective nitrogen content of each portion located closer to the surface of the phase change material, and higher than a respective nitrogen content of each portion located farther from the surface of the phase change material.

7. The memory cell of claim 1, wherein each portion of the plurality of portions of material is a discrete layer of material.

8. The memory cell of claim 7, wherein the plurality of portions of material comprises more than two discrete layers of material.

9. The memory cell of claim 1, further comprising:
wherein the surface of the phase change material extends beyond opposing edges of the surface of the second electrode; and

wherein a cross-section of each individual portion is larger than a respective cross-section of each portion located closer to the surface of the phase change material, and smaller than a respective cross-section of each portion located farther from the surface of the phase change material.

10. The memory cell of claim 9, wherein each cross-section is taken in a direction parallel to the surface of the phase change material.

11. The memory cell of claim 9, wherein the second electrode has a conical-like shape.

12. The memory cell of claim 1, wherein the surface of the phase change material is a first surface of the phase change material, and wherein the surface of the first electrode extends from an edge of the phase change material extending orthogonally from a second surface of the phase change material facing the surface of the first electrode to an opposing edge of the phase change material extending orthogonally from the second surface of the phase change material.

13. The memory cell of claim 12, wherein the first surface of the phase change material extends beyond opposing edges of the surface of the second electrode.

14. The memory cell of claim 12, wherein the surface of the second electrode extends beyond opposing edges of the first surface of the phase change material.

15. A memory cell, comprising:
a first electrode having a surface;
a second electrode having a surface facing the surface of the first electrode; and

a phase change material between the first electrode and the second electrode, the phase change material having a first surface facing the first electrode and having a second surface in contact with the surface of the second electrode;

wherein the second electrode comprises a plurality of layers of material, each layer having a respective distance

from the second surface of the phase change material and each layer having a respective resistivity;

wherein a layer of the plurality of layers of material farthest from the second surface of the phase change material has a lowest resistivity of the plurality of layers of material and a layer of the plurality of layers of material closest to the second surface of the phase change material has a highest resistivity of the plurality of layers of material; wherein the resistivity of each individual layer is lower than the resistivity of each layer located closer to the second surface of the phase change material, and higher than the resistivity of each layer located farther from the second surface of the phase change material; and

wherein a surface area of the surface of the second electrode is larger than a surface area of the second surface of the phase change material.

16. The memory cell of claim 15, wherein a surface area of the first surface of the phase change material is greater than the surface area of the second surface of the phase change material.

17. A memory cell, comprising:
a first electrode having a surface;
a second electrode having a surface facing the surface of the first electrode; and

a phase change material between the first electrode and the second electrode and having a surface facing the surface of the second electrode;

wherein the second electrode comprises a plurality of layers of material, each layer having a respective distance from the surface of the phase change material and each layer having a respective resistivity;

wherein a layer of the plurality of layers of material farthest from the surface of the phase change material has a lowest resistivity of the plurality of layers of material and a layer of the plurality of layers of material closest to the surface of the phase change material has a highest resistivity of the plurality of layers of material;

wherein the resistivity of each individual layer is lower than the resistivity of each layer located closer to the surface of the phase change material, and higher than the resistivity of each layer located farther from the surface of the phase change material; and

wherein a surface area of the surface of the second electrode is smaller than a surface area of the surface of the phase change material.

18. The memory cell of claim 17, wherein the surface of the second electrode is in contact with the surface of the phase change material.

19. The memory cell of claim 17, wherein a cross-section of each individual layer is larger than a respective cross-section of each layer located closer to the surface of the phase change material, and smaller than a respective cross-section of each layer located farther from the surface of the phase change material.

20. The memory cell of claim 19, wherein a thermal conductivity of each individual layer is higher than a respective thermal conductivity of each layer located closer to the surface of the phase change material, and lower than a respective thermal conductivity of each layer located farther from the surface of the phase change material.